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(54) **Projection exposure apparatus and device manufacturing method**

Apparat zur Projektionsbelichtung und Verfahren zur Herstellung einer Vorrichtung

Appareil d'exposition par projection et méthode de fabrication d'un dispositif

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Description

[0001] This invention relates to a projection exposure apparatus and a device manufacturing method. Specifically, the invention is suitably usable in manufacture of devices with patterns of a size of submicron or quartermicron order or smaller, such as ICs, LSIs, CCDs or liquid crystal panels, for example, based on a projection optical system with a diffractive optical element for projecting and printing a device pattern of a reticle or mask (hereinafter "mask") on different regions on a wafer through a step-and-repeat procedure or step-and-scan procedure.

[0002] Many proposals have recently been made in relation to an optical system having a diffractive optical element. Examples are "SPIE, Vol. 1353, pp 297-309, International Lens Design Conference (1990)", Japanese published patent applications, 4213421, 6324262 and 6331941, and U.S. Patent No. 5,044,706, wherein a phenomenon that chromatic aberration of a diffractive optical element is inverse to that of an ordinary refractive lens element is utilized and wherein a diffractive optical element having a positive optical power is formed on the surface of a lens or transparent plate to reduce the chromatic aberration of the optical system.

[0003] Further, proposals have been made in respect to a diffractive optical element called "binary optics element" wherein the units constituting the element are defined by a step-structure of two levels or more. Examples are "G.J. Swanson, Technical Report 854, MIT Lincoln Laboratory, 14, Aug. 1989" and "G.J. Swanson, Technical Report 914, MIT Lincoln Laboratory, 1 May 1991".

[0004] On the other hand, proposals have been made in respect to a projection exposure apparatus for manufacture of semiconductor devices, which uses a diffractive optical element for correction of aberrations. Examples are Japanese published patent applications 6331941, 7128590 and 8017719. In these proposals, a projection optical system includes one or more diffractive optical elements mainly for correction of axial chromatic aberration or magnification chromatic aberration.

[0005] In respect to efficiency of use of light, use of a phase type diffractive optical element may be preferable. In a phase type diffractive optical element, if its kinoform is defined idealistically, it shows a diffraction efficiency of 100%. In a binary optics element, as compared therewith, since its kinoform is defined by approximation with steps, it does not show a diffraction efficiency of 100% even though the element is formed idealistically. With a structure of eight steps, for example, a highest diffraction efficiency will be about 95%. Thus, diffraction light (unwanted diffraction light) not contributable to the imaging, will be produced. Such unwanted diffraction light is not correctly imaged at a desired position, and it produces flare light which reaches the image plane and deteriorates the image quality.

[0006] In an occasion where a diffractive optical element produces unwanted diffraction light such as described above, there are two possibilities: that is, a case in which the unwanted diffraction light is reflected once or more by an inside wall of a lens barrel until it reaches the image plane; and a case in which it passes through the effective diameter of the optical system without such reflection. According to the investigations made by the inventors, it has been found that: of these two types of unwanted diffraction lights, the unwanted diffraction light which is reflected by the lens barrel can be reduced in its intensity to a level that can be disregarded, by means of barrel design or anti-reflection treatment to the inside wall of the barrel; whereas the unwanted diffraction light that directly passes through the effective diameter of the optical system may cause non-uniform exposure.

[0007] When the effect of unwanted diffraction light upon the image quality is to be evaluated, both of (i) the intensity of unwanted diffraction light relative to the diffraction light of design order or orders (the intensity of regular diffraction light to be used for the imaging), upon the image plane, as well as (ii) the intensity distribution of the unwanted diffraction light upon the image plane, should be considered. Of course, it is desirable that the intensity of unwanted diffraction light upon the image plane is nearly equal to zero. However, to accomplish it is very difficult. Through the investigations made by the inventors, it has been found that, even if there is unwanted diffraction light having an intensity a few percent of the intensity of diffraction light of design orders, there occurs substantially no adverse effect to the image quality provided that the intensity distribution of the unwanted light on the image plane is approximately uniform.

[0008] It is accordingly an object of the present invention to provide a unique and improved projection exposure apparatus and a device manufacturing method using the same.

[0009] In accordance with a first aspect of the present invention, there is provided a projection exposure apparatus, comprising:

an illumination optical system for illuminating a mask with light from a light source; and
a projection optical system having at least one diffractive optical element, for projecting an image of a pattern of the illuminated mask onto a substrate, wherein said at least one diffractive optical element is adapted to produce first diffraction light of a first predetermined diffraction order for projecting the image, and second diffraction light of a diffraction order different from that of the first diffraction light, wherein an intensity distribution upon the substrate of that portion of the second diffraction light to be superimposed on the image of the pattern upon the substrate is substantially uniform.

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Said first and second diffractive optical elements may have a relative ratio, not greater than 2.5, of frequencies fR_1 and fR_2 their diffraction gratings at the largest effective diameter.

[0010] Embodiments of the present invention will now be described with reference to the accompanying drawings, in which:

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Figure 1 is a schematic view of a main portion of a projection optical system according to a first embodiment of the present invention.

Figure 2 shows spherical aberration, astigmatism and distortion of the projection optical system of the first embodiment of the present invention.

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Figure 3 shows lateral aberration of the projection optical system of the first embodiment of the present invention.

Figure 4 shows intensity distribution of unwanted diffraction light as defined on an image plane by the projection optical system of the first embodiment of the present invention.

Figure 5 is a schematic view of a main portion of a projection optical system according to a second embodiment of the present invention.

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Figure 6 shows spherical aberration, astigmatism and distortion of the projection optical system of the second embodiment of the present invention.

Figure 7 shows lateral aberration of the projection optical system of the second embodiment of the present invention.

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Figure 8 shows intensity distribution of unwanted diffraction light as defined on an image plane by the projection optical system of the second embodiment of the present invention.

Figure 9 is a schematic view of a main portion of a projection optical system according to a third embodiment of the present invention.

Figure 10 shows spherical aberration, astigmatism and distortion of the projection optical system of the third embodiment of the present invention.

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Figure 11 shows lateral aberration of the projection optical system of the third embodiment of the present invention.

Figure 12 shows intensity distribution of unwanted diffraction light as defined on an image plane by the projection optical system of the third embodiment of the present invention.

Figure 13 is a schematic view of a main portion of a projection optical system to be compared with the present invention.

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Figure 14 shows aberrations of a projection optical system to be compared with the present invention.

Figure 15 shows lateral aberration of a projection optical system to be compared with the present invention.

Figure 16 shows intensity distribution of unwanted diffraction light as defined on an image plane by a projection optical system to be compared with the present invention.

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Figure 17 is a schematic view of a main portion of another projection optical system to be compared with the present invention.

Figure 18 shows aberrations of a projection optical system to be compared with the present invention.

Figure 19 shows lateral aberration of a projection optical system to be compared with the present invention.

Figure 20 shows intensity distribution of unwanted diffraction light as defined on an image plane by a projection optical system to be compared with the present invention.

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Figure 21 is a graph for explaining the relation between effective radius and frequency of a diffractive optical element in the first embodiment of the present invention.

Figure 22 is a graph for explaining the relation between effective radius and frequency of a diffractive optical element in the second embodiment of the present invention.

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Figure 23 is a graph for explaining the relation between effective radius and frequency of a diffractive optical element in the third embodiment of the present invention.

Figure 24 is a graph for explaining the relation between effective radius and frequency of a diffractive optical element in a projection optical system to be compared with the present invention.

Figure 25 is a graph for explaining the relation between effective radius and frequency of a diffractive optical element in another projection optical system to be compared with the present invention.

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Figure 26 is a schematic view for explaining unwanted diffraction light.

Figure 27 is a flow chart for explaining the procedure of optical designing method and optical system producing method, according to the present invention.

Figure 28 is a flow chart of a device manufacturing method according to the present invention.

Figure 29 is a flow chart of a wafer process according to the present invention.

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[0011] Figure 1 is a schematic view of a main portion of a projection exposure apparatus according to a first embodiment of the present invention. In this embodiment, the invention is applied to a projection exposure of step-and-repeat type or step-and-scan type for lithographic process of submicron or quartermicron order or less. This is also the case

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with other embodiments to be described later. Denoted in the drawing at PL is a projection optical system. The illustration shows a state in which a first object such as a reticle or mask M (hereinafter "mask") having an electronic circuit pattern formed thereon is illuminated with exposure light from an illumination device ED, comprising a light source and an illumination optical system, and in which the device pattern of the first object M is projected by the projection optical system PL on a shot region of a second object such as a wafer W (silicon substrate), in a reduced scale. The light source may comprise a KrF excimer laser, ArF excimer laser or F₂ laser, for example.

[0012] Denoted at SP is a stop (aperture stop) which determines the pupil plane of the projection optical system PL. Denoted at BOE1 and BOE2 are first and second diffractive optical elements formed on the surfaces of lenses, respectively. Each diffractive optical element comprises a binary optics element. These diffractive optical elements BOE1 and BOE2 are provided on the corresponding lenses so that they are placed adjacent to the pupil plane SP and that they sandwich the pupil plane therebetween.

[0013] This embodiment employs such structure that the first and second diffractive optical elements BOE1 and BOE2 each having a predetermined diffraction grating structure are disposed adjacent to and before and after the pupil plane of the projection optical system PL. This enables superior correction of aberrations including chromatic aberration. Additionally, adverse effect (e.g., non-uniform exposure) on the image plane (shot region) due to the flare component resulting from unwanted diffraction light to be provided by the provision of the diffractive optical elements, can be reduced or avoided.

[0014] Figure 26 illustrates unwanted diffraction light produced by one diffractive optical element BOE. The unwanted diffraction light comprises diffraction light of a diffraction order or orders different from the order or orders of predetermined diffraction light which is to be used for formation of an image of the pattern of the first object M. A portion of the unwanted diffraction light is not projected on the substrate W, but is incident on the inside wall of the lens barrel and is absorbed thereby. The remaining portion of the unwanted light impinges on the substrate W. In the present invention, in order to avoid non-uniformness of exposure, the structure is arranged to assure that the unwanted diffraction light impinging on the substrate W provides substantially uniform light intensity distribution within the shot region on the substrate.

[0015] Each of the first and second diffractive optical elements BOE1 and BOE2 is made of a material of quartz. Also, the projection optical system PL comprises lenses of a single glass material of quartz or fluorite, or glass materials of quartz and fluorite. Specifically, in the embodiments described below, all of the diffractive optical elements and lenses may be provided by a single glass material of quartz.

[0016] In this embodiment, two diffractive optical elements which satisfy the above-described conditions, i.e., equations (1) and (2) or equations (1') and (2'), may be used. Alternatively, only one diffractive optical element which satisfies these conditions or three diffractive optical elements satisfying the conditions, may be used.

[0017] In this embodiment, the pattern (device pattern) of the first object M as illuminated with exposure light from the illumination device ED is projected by the projection optical system PL on to the second object (wafer) W. After this, the exposed wafer is processed by a development treatment, and semiconductor devices are produced.

[0018] The diffractive optical elements BOE1 and BOE2 according to this embodiment will be explained. The projection optical system PL of this embodiment uses phase type diffractive optical elements as the first and second diffractive optical elements BOE1 and BOE2. It is known that, with a phase type diffractive optical element, if it has an idealistically produced kinoform, it can provide 100% diffraction efficiency (the intensity ratio of the light as deflected and transmitted in a desired direction, to the light incident on the diffractive optical element).

[0019] In the phase type diffractive optical element used in this embodiment, the phase of light impinging on the diffractive optical element is changed by an amount corresponding to the applied phase function, by which deflection toward a desired direction is accomplished. Here, the phase function can be defined as a function of position upon the diffractive optical element.

[0020] Usually, a diffractive optical element is revolutionally symmetric. Thus, the phase function is a function of distance r from the optical axis. For example, the phase function $\phi(r)$ of an aberration-free lens having a focal length f is given by:

$$\phi(r) = -(2\pi/\lambda)(\sqrt{r^2 + f^2} - f)$$

where λ is the wavelength of light used.

[0021] While the phase function $\phi(r)$ represents the phase, in order to realize this phase change with the diffractive optical element it is represented by an optical path length (optical path length function) $\text{opl}(r)$. The optical path length $\text{opl}(r)$ necessitates dividing the phase function $\phi(r)$ by 2π . Here, the unit of length is the wavelength λ .

$$\text{opl}(r) = -(\sqrt{r^2 + f^2} - f)/\lambda$$

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[0022] Regarding the shape of a diffractive optical element that provides this optical path length $\text{opl}(r)$, if it is in an air and the refractivity of the glass material with the wavelength λ is n , the shape $F(r)$ is given by:

$$F(r) = -(\sqrt{r^2 + f^2} - f)/[\lambda(n-1)]$$

[0023] Basically, the shape $F(r)$ above represents the surface shape of a refractive optical element. A diffractive optical element uses a phenomenon that the phase term of light corresponds to a period 2π . First, such $r=R_m$ (m is an integer: $R_0=0$, and it is counted sequentially from the optical axis toward the outside) of a value which corresponds, in terms of phase function $\phi(r)$, to a product of 2π by an integer is calculated, and then a phase function wherein a product of 2π by an integer is added so that the value in the period $[R_m, R_{m+1}]$ comes into the range $[0, 2\pi]$, is prepared. This corresponds to that, with the optical path length function $\text{opl}(r)$, it goes into the range $[0, 1]$ in the period $[R_m, R_{m+1}]$.

[0024] Thus, an aberration-free lens based on a diffractive optical element can be provided by applying the surface shape to the diffractive optical element on the basis of a function as dividing by $(n-1)$ the optical path length function $\text{opl}(r)$ where the value range is $[0, 1]$. Usually, a diffractive optical element whose diffraction effect is provided by the surface shape of the element (i.e., surface protrusions and grooves) is called "surface relief type".

[0025] In a phase type diffractive optical element, a desired aspherical surface effect can be provided by the manner of applying the phase function $\phi(r)$. Also, since the value range of the optical path length function $\text{opl}(r)$ is $[0, 1]$, the depth of necessary surface shape $F(r)$ is of an order of wavelength. Thus, the diffractive optical element can be made thin. Additionally, since deflection of light through diffraction by a diffractive optical element becomes larger with longer wavelength, it provides opposite color dispersion characteristic to a refractive optical element of ordinary glass material. Thus, when a refractive optical element and a diffractive optical element are used in combination, correction of chromatic aberration can be done without use of different glass materials. The diffractive optical elements BOE1 and BOE2 of the first embodiment of Figure 1 may be based on these features, as desired.

[0026] In this embodiment, the features as described above are applied to a projection optical system of semiconductor device manufacturing projection exposure apparatus of step-and-repeat or step-and-scan type.

[0027] Currently, the wavelength of exposure light usable with a projection optical system of a stepper is mainly light of i-line ($\lambda = 365$ nm). Additionally, there are cases where light of ultraviolet region such as, for example, KrF excimer laser ($\lambda = 248$ nm) or next generation ArF excimer laser ($\lambda = 193$ nm) is used as exposure light. The glass material which has sufficient transmissivity to light of such ultraviolet region is limited to SiO_2 and CaF_2 only. Particularly, the glass material for a projection optical system usable with light of F_2 laser is CaF_2 only.

[0028] Since the type of glass material usable for a refractive optical element is limited as described, when a projection optical system to be used with exposure light of ultraviolet region is provided only by refractive optical elements, correction of chromatic aberration is difficult to accomplish. Also, for correction of chromatic aberration, strict condition is applied in respect to the bandwidth of the light source. Further, the number of lenses becomes larger because of required aberration correction, assuring the optical performance. This results in an increase of total thickness of lenses and thus in degraded transmissivity of the whole optical system. The decrease of transmissivity, that is, the increase of absorption by lenses, is undesirable from the viewpoint of exposure aberration.

[0029] In this embodiment, the problems of chromatic aberration and increased total thickness of lenses in a projection optical system to be used with exposure light of ultraviolet region, can be solved by providing a diffractive optical element of appropriate shape at the position of or adjacent to the pupil position of the projection optical system. Thus, in this embodiment, non-uniform exposure is substantially avoided.

[0030] A diffractive optical element usable in this embodiment may be produced, not by directly forming an idealistic shape (blazed shape or kinoform shape) on a transparent substrate, but by approximating such idealistic shape with stepped shape (with levels). Although directly forming a blazed shape or kinoform shape is difficult in the point of required machining precision, for example, in this embodiment a stepper may be used for production of a diffractive optical element to be used. This facilitates manufacture of a diffractive optical element of fine structure.

[0031] Since a diffractive optical element used in this embodiment has a shape approximating the idealistic shape with level structure, the diffraction efficiency does not reach 100% and there is small unwanted diffraction light produced.

[0032] If the number of steps (levels) is N and the diffraction order (design order) of diffraction light being diffracted in a desired deflection direction is 1, the diffraction efficiency η_m^N of diffraction light of a diffraction order m other than 1 is expressed as follows:

$$\eta_m^N = \frac{[\sin(\pi m/N) \sin(\pi(1-m))]^2}{[\pi m \sin(\pi(1-m)/N)]^2}$$

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The above is based on an assumption that the depth of relief of the diffractive optical element has been optimized. Here, if 1 is substituted into m of the above equation, then $\eta_1^0 = 1$ results. From this, it is seen that in an idealistic case where the depth is optimized, the diffraction efficiency is 100%. Practically, from the precision of machining and diffraction efficiency, N may be set to about 8 to 16. Preferably, from the standpoint of manufacture, N may be set to about 8. In that occasion, the diffraction efficiency is $\eta_1^0 = 0.95$. Further, η_m^0 has a value only with $m = \dots, -15, -7, 1, 9, 17, \dots$, and thus the following is given:

$$\eta_m^0 = [\sin(\pi m/8)/(\pi m/8)]^2$$

[0033] Examples are $\eta_9^0 = 0.117$ and $\eta_{17}^0 = 0.0033$. Namely, with a diffractive optical element of eight steps (levels), unwanted diffraction light appears in the order represented by $m = 8n+1$ (n is an integer other than 0). Similarly, if the precision of approximation is enhanced and the element has steps of a number sixteen ($N = 16$), unwanted diffraction light will appear in the order represented by $m = 16n+1$ (n is an integer other than 0).

[0034] As described, when a diffractive optical element is used, there is unwanted diffraction light produced. The unwanted diffraction light does not satisfy the imaging condition, and thus when it is incident on the image plane, it produces a flare component. This causes non-uniformness of exposure and degradation of image quality. It is therefore desirable to prevent, as much as possible, impingement of (unwanted) diffraction light of order $m = \dots, -15, -7, 9, 17, \dots$ (in the case of diffractive optical element with eight steps) or (unwanted) diffraction light of order $m = \dots, -31, -15, 17, 33, \dots$ (in the case of diffractive optical element with sixteen steps), onto a predetermined area on the image plane (shot area on the wafer).

[0035] In conventional projection optical systems having a diffractive optical element, focus is put on correction of aberration only. There is no attention given to the effect of unwanted diffraction light.

[0036] In an optical designing method according to the present invention, when it is applied to designing an optical system having a diffractive optical element and lenses, the procedure includes as shown in Figure 27 (i) a first step for determining the position of the diffractive optical element with respect to an optical path so that, within a predetermined range on an imaging plane defined by the optical system, predetermined diffraction light of a predetermined order from the diffractive optical element and being contributable to the imaging and unwanted diffraction light not contributable to the imaging have a substantially constant ratio, and (ii) a second step for determining optical constants such as curvature and thickness, for example, of the diffractive optical element and lenses in accordance with the determination at the first step.

[0037] The present embodiment and other embodiments to be described may be based on this optical designing method.

[0038] Also, in a method of producing an imaging optical system, for use in a lithographic process, having a diffractive optical element, a refractive optical element and/or a reflective optical element, according to the present invention, as shown in Figure 27, in optical designing, the position of the diffractive optical element is determined so that, as compared with a different position, an undesirable effect, to an image plane, of diffraction light from the diffractive optical element of an order other than a design order is reduced, and then optical constants such as curvature and thickness, for example, of the diffractive optical element, the refractive optical element and/or the reflective optical element are determined.

[0039] The refractive optical element and/or the reflective optical element may have an aspherical surface, and the undesirable effect may be non-uniformness of exposure. The position with less undesirable effect may be the position at or adjacent to the aperture stop, and the diffractive optical element may be disposed there.

[0040] In this embodiment, at least two diffractive optical elements may be disposed adjacent to the aperture stop within the projection optical system, by which superior aberration correction is assured and undesirable effect of unwanted diffraction light is prevented.

[0041] The two diffractive optical elements may be disposed so as to satisfy the two conditions of equations (1) and (2) described above. This reduces non-uniformness of exposure, and assures good optical performance.

[0042] The condition of equation (1) is to geometrically restrict the distance d between the pupil (aperture stop) and the first or second diffractive optical element. The condition of equation (2) is to restrict extension of largest light ray, determining the numerical aperture (NA), from the object point, with respect to the surface of the first or second diffractive optical element.

[0043] If one of the upper and lower limits of the conditions of equations (1) and (2) is exceeded, it becomes difficult to reduce non-uniformness of exposure on the image plane (shot area on the substrate).

[0044] In the present invention, at least two diffractive optical elements are provided within the projection optical system, and they are disposed adjacent to the pupil plane (i.e. aperture stop SP) of the projection optical system. With this arrangement, unwanted diffraction light is added, upon the image plane, to the regular image (mask pattern image) as background light having substantially uniform light intensity distribution. While the contrast of the image may reduce

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slightly, substantially uniform contrast is provided over the whole image plane and, therefore, it can be met by a process to be done later.

[0045] In this embodiment, optical path length function $opl(r)$ is used to describe the characteristic of diffractive optical element (binary optics element).

[0046] If the distance from the optical axis of the diffractive optical element is denoted by r ,

$$opl(r) = (C_1 r^2 + C_2 r^4 + C_3 r^6) / \lambda_p$$

is used and, based on this, the coefficients C_1 , C_2 and C_3 as well as the wavelength λ are given. Here, the wavelength λ_p is one called production wavelength. In designing, it may be the same as or different from the wavelength to be actually used in the optical system. In this embodiment, the exposure light used may have a bandwidth not greater than several hundred picometers (300 pm).

[0047] As regards the aspherical surface shape, it is determined on the basis of:

$$z(r) = [cr^2 / \{1 + \sqrt{1 - (1+K)c^2 r^2}\}] + Ar^4 + Br^6 + Cr^8 + Dr^{10} + Er^{12} + Fr^{14}$$

and by giving K , c , A , B , C , D , E and F , wherein c is the curvature radius.

[0048] A numerical example of the projection optical system according to the first embodiment of the present invention will be described below.

[Numerical Example 1]

[0049] Object Height: 0mm, 35mm, 50mm NA=0.50 λ =193.00nm

Surface Number	Curvature Radius	Surface Spacing	Refractivity (λ =193.00nm)
OBJ	INFINITY	148.52	1.0
1	630.31	15.00	1.560772
2	220.99	36.235	1.0
	(aspherical) K: -2.28		
	A: 0.226 E-07	B: 0.715 E-12	C: -0.299 E-16
	D: 0.634 E-20	E: -0.168 E-23	F: 0
3	290.81	30.00	1.560772
	(aspherical) K: -0.0262		
	A: -0.214 E-08	B: 0.369 E-12	C: -0.933 E-17
	D: -0.141 E-20	E: -0.907 E-25	F: 0
4	-572.22	36.339	1.0
5	466.213	30.00	1.560772
6	-407.87	164.326	1.0
7	123.981	13.00	1.560772
8	110.516	15.00	
	(aspherical) K: 0.000000		
	A: 0.167 E-07	B: 0.208 E-10	C: 0.783 E-14
	D: -0.386 E-18	E: 0.347 E-22	F: 0
9	1546.52	13.00	1.560772
10	174.68	21.00	1.0
	(aspherical) K: -0.972		
	A: -0.233 E-07	B: -0.612 E-10	C: -0.145 E-13
	D: -0.362 E-17	E: 0.265 E-20	F: 0

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(continued)

Surface Number	Curvature Radius	Surface Spacing	Refractivity ($\lambda=193.00\text{nm}$)
11	-140.57862 (aspherical) K: 4.804 A: -0.153 E-06 D: -0.744 E-17	13.000000 B: -0.903 E-11 E: 0.512 E-20	1.560772 C: 0.852 E-14 F: 0
12	125.62	108.47	1.0
13	-660.11 (BOE) Design Order -1 $\lambda_p=632.80\text{nm}$ C1: 3.24 E-03	35.00 C2: -4.34 E-09	1.560772 C3: 2.08 E-13
14	-172.686 (aspherical) K: 0.0130 A: -0.693 E-09 D: -0.615 E-22	1.00 B: 0.377 E-13 E: -0.247 E-25	1.0 C: 0.192 E-17 F: 0.955304E-30
15	STOP INFINITY	32.000000	
16	424.39 (aspherical) K: 0.437 A: 0.675 E-09 D: -0.758 E-22	37.00 B: 0.905 E-15 E: -0.386 E-26	1.560772 C: -0.521 E-18 F: -0.153 E-30
17	-729.28 (BOE) Design Order -1 $\lambda_p=632.80\text{nm}$ C1: 1.714 E-03	119.71 C2: -1.654 E-09	1.0 C3: -2.586 E-13
18	109.24 (aspherical) K: -0.212307 A: 0.762 E-09 D: -0.346 E-20	30.00 B: -0.470 E-12 E: -0.158 E-23	1.560772 C: -0.145600E-15 F: 0
19	462.671	39.20	1.0
20	139.22	30.00	1.560772
21	128.21 (aspherical) K: 1.26 A: 0.180 E-06 D: -0.115 E-16	32.28 B: 0.746 E-12 E: 0.481 E-20	1.0 C: -0.270 E-13 F: 0
IMG	IMAGE INFINITY PLANE	0.001225	

[0050] Figures 2 and 3 illustrate aberrations of Numerical Example 1.

[0051] Irrespective of that the optical system is provided by a single glass material, all of these aberrations including chromatic aberration are corrected satisfactorily, and the effect of the diffractive optical elements well appears.

[0052] Figure 4 shows an intensity distribution of unwanted diffraction light upon the image plane, in this embodiment, wherein the intensity of unwanted light is illustrated as being standardized with respect to the intensity of diffraction light of design order.

[0053] Calculation of unwanted diffraction light here is based on that there is a circular opening of a radius 50 mm on the object plane and the luminance distribution and light orientation distribution are uniform over the whole circular opening, and that each of two diffractive optical elements has a step structure of eight levels. It is seen from Figure 4 that in this embodiment the intensity ratio of the unwanted diffraction light to the diffraction light of design order is about 0.1% and it is substantially uniform over the whole image plane, and that the effect of the unwanted diffraction light is very small.

[0054] Figure 21 shows the relation between the effective radius of the diffractive optical element and the frequency, in this embodiment.

[0055] Figure 5 is a schematic view of a main portion of an optical system according to a second embodiment of the

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present invention. This embodiment differs from the first embodiment of Figure 1 in the point that diffractive optical elements BOE1 and BOE2 are provided on the surfaces of two lenses which are disposed on one side of the aperture stop SP, facing the image plane. The remaining portion has essentially the same structure.

[0056] Both of the diffractive optical elements used in this embodiment are disposed in the neighbourhood of the pupil and on the image plane side thereof. Figures 6 and 7 show aberrations of a numerical example (Numerical Example 2) according to this embodiment, to be described below. Although the optical system is provided by a single glass material, aberrations including chromatic aberration are well corrected.

[0057] Figure 8 shows an intensity distribution of unwanted diffraction light upon the image plane, in this embodiment, wherein the intensity of unwanted light is illustrated as being standardized with respect to the intensity of diffraction light of design order. Calculation of unwanted diffraction light here is based on that there is a circular opening of a radius 50 mm on the object plane and the luminance distribution and light orientation distribution are uniform over the whole circular opening, and that each of two diffractive optical elements has a step structure of eight levels.

[0058] It is seen from Figure 8 that in this embodiment the intensity ratio of the unwanted diffraction light to the diffraction light of design order is about 0.11% and it is substantially uniform over the whole image plane, and that the effect of the unwanted diffraction light is very small.

[0059] Figure 22 shows the relation between the effective radius of the diffractive optical element and the frequency, in this embodiment.

[0060] Next, a numerical example (Numerical Example 2) according to this embodiment will be described.

[Numerical Example 2]

[0061] Spec.: Magnification=1/4, NA=0.50 λ =193.00nm

Surface Number	Curvature Radius	Surface Spacing	Refractivity (λ =193.00nm)
OBJ	INFINITY	110.522	1.0
1	709.86	15.00	1.560772
2	165.02	80.486	1.0
	(aspherical) K: -2.83		
	A: 0.186 E-07	B: 0.806 E-12	C: -0.525 E-16
	D: 0.434 E-19	E: -0.156 E-22	F: 0
3	308.74	40.00	1.560772
	(aspherical) K: 0.102		
	A: -0.167 E-08	B: 0.788 E-12	C: -0.274 E-16
	D: -0.351 E-20	E: 0.354 E-25	F: 0
4	-313.98	17.21	1.0
5	246.56	25.00	1.560772
6	946.85	89.50	1.0
7	87.38	13.00	1.560772
8	84.94	15.00	1.0
	(aspherical) K: 0.000000		
	A: -0.128 E-08	B: 0.182 E-10	C: 0.746 E-14
	D: 0.288 E-19	E: -0.279 E-22	F: 0
9	-4922.29	13.00	1.560772
10	178.10	21.00	1.0
	(aspherical) K: -2.34		
	A: -0.481 E-07	B: -0.638 E-10	C: -0.104 E-13
	D: -0.200 E-17	E: 0.231 E-20	F: 0
11	-136.04	13.000000	1.560772
	(aspherical) K: 4.64		
	A: -0.142 E-06	B: 0.361 E-12	C: 0.143 E-13
	D: -0.549 E-17	E: 0.469 E-20	F: 0

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(continued)

	Surface Number	Curvature Radius	Surface Spacing	Refractivity ($\lambda=193.00\text{nm}$)
5	12	141.97	109.83	1.0
	13	-603.93	35.00	1.560772
		(aspherical) K: 0.154		
		A: -0.111 E-09	B: -0.399 E-13	C: -0.144 E-17
10		D: 0.397 E-21	E: -0.247 E-25	F: 0.977 E-25
	14	-163.49	1.00	1.0
		(aspherical) K: 0.026		
		A: -0.111 E-08	B: 0.203 E-14	C: -0.140 E-17
15		D: 0.136 E-23	E: 0.424 E-25	F: 0.347 E-29
	15	STOP INFINITY	32.000000	1.0
		(Stop)		
	16	512.45	37.00	1.560772
		(aspherical) K: 0.478		
20		A: 0.785 E-09	B: 0.260 E-14	C: 0.692 E-18
		D: 0.293 E-22	E: 0.178 E-26	F: -0.497 E-30
	17	-564.67	21.55	1.0
		(BOE) Design Order -1 $\lambda_p=632.80\text{nm}$		
25		C1: 2.146 E-03	C2: -4.714 E-10	C3: -1.840 E-13
	18	1750.00	20.00	1.560772
	19	629.89	142.99	1.0
		(BOE) Design Order -1 $\lambda_p=632.80\text{nm}$		
30		C1: 1.935 E-03	C2: 1.153 E-09	C3: 1.174 E-13
	20	108.30	35.00	1.560772
		(aspherical) K: -0.212		
		A: -0.762 E-09	B: -0.470 E-12	C: -0.146 E-15
35		D: -0.346 E-20	E: -0.157 E-23	F: 0
	21	405.11	40.57	1.0
	22	121.43	30.00	1.560772
	21	155.76	30.39	1.0
		(aspherical) K: -0.167		
40		A: 0.114 E-06	B: -0.283 E-10	C: 0.251 E-13
		D: -0.804 E-16	E: 0.414 E-19	F: 0
	24	STOP INFINITY (IMG)	0.000939	

[0062] Figure 9 is a schematic view of a main portion of an optical system according to a third embodiment of the present invention. This embodiment differs from the first embodiment of Figure 1 in that diffractive optical elements BOE1 and BOE2 are provided on the surfaces of lenses which are disposed on the object side of the aperture stop SP. The remaining portion has essentially the same structure.

[0063] Figures 10 and 11 show aberrations of a numerical example (Numerical Example 3) according to this embodiment, to be described below. Although the optical system is provided by a single glass material, aberrations including chromatic aberration are well corrected.

[0064] Figure 12 shows an intensity distribution of unwanted diffraction light upon the image plane, in this embodiment, wherein the intensity of unwanted light is illustrated as being standardized with respect to the intensity of diffraction light of design order. Calculation of unwanted diffraction light here is based on that there is a circular opening of a radius 50 mm on the object plane and the luminance distribution and light orientation distribution are uniform over the whole circular opening, and that each of two diffractive optical elements has a step structure of eight levels.

[0065] It is seen from Figure 12 that in this embodiment the intensity ratio of the unwanted diffraction light to the

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diffraction light of design order is about 0.13% and it is substantially uniform over the whole image plane, and that the effect of the unwanted diffraction light is very small.

[0066] Figure 23 shows the relation between the effective radius of the diffractive optical element and the frequency, in this embodiment.

5 [0067] Next, a numerical example (Numerical Example 3) according to this embodiment will be described.

[Numerical Example 3]

10 [0068] Spec.: Magnification=1/4, NA=0.50 λ =193.00nm

Surface Number	Curvature Radius	Surface Spacing	Refractivity (λ =193.00nm)
OBJ	INFINITY	147.377	1.0
1	-4548.42	15.00	1.560772
2	148.52	93.24	1.0
	(aspherical) K: -2.33		
	A: 0.860 E-08	B: -0.138 E-11	C: 0.121 E-15
	D: 0.228 E-19	E: -0.661 E-23	F: 0
3	423.51	30.00	1.560772
	(aspherical) K: -1.266		
	A: -0.699 E-08	B: -0.112 E-12	C: 0.818 E-17
	D: 0.103 E-20	E: 0.276 E-25	F: 0
4	-474.05	0.21	1.0
5	198.61	30.00	1.560772
6	-808.86	131.96	1.0
7	-208.81	13.00	1.560772
8	128.08	15.00	1.0
	(aspherical) K: 0.000000		
	A: -0.254 E-07	B: 0.251 E-10	C: 0.957 E-14
	D: 0.459 E-18	E: -0.477 E-21	F: 0
9	206.71	18.00	1.560772
10	-710.89	21.00	1.0
	(aspherical) K: 109.58		
	A: -0.591 E-07	B: -0.569 E-10	C: -0.126 E-13
	D: -0.115 E-17	E: 0.189 E-20	F: 0
11	-142.69	13.000000	1.560772
	(aspherical) K: 4.75		
	A: -0.109 E-06	B: 0.208 E-10	C: 0.117 E-13
	D: -0.838 E-17	E: 0.522 E-20	F: 0
12	122.15	70.97	1.0
13	INFINITY	25.00	1.560772
	(BOE) Design Order -1 λ p=632.80nm		
	C1: 1.997 E-03	C2: 8.375 E-10	C3: -1.522 E-13
14	-437.15	9.21	1.0
15	-717.05	40.00	1.560772
	(BOE) Design Order -1 λ p=632.80nm		
	C1: 3.000 E-03	C2: -2.263 E-09	C3: 2.118 E-13
16	-185.12	5.00	1.560772
	(aspherical) K: -0.0028		
	A: 0.604 E-09	B: 0.148 E-12	C: 0.905 E-17

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(continued)

Surface Number	Curvature Radius	Surface Spacing	Refractivity ($\lambda=193.00\text{nm}$)
17	D: 0.253 E-21 STOP INFINITY (Stop)	E: -0.145 E-25 10.000000	F: -0.781 E-30 1.0
18	534.58 (aspherical) K: -0.778	37.00	1.560772
19	A: 0.177 E-09 D: -0.113 E-21 -589.91 (aspherical) K: -0.9515	B: -0.933 E-13 E: -0.398 E-26 113.05	C: -0.568 E-17 F: -0.716 E-29 1.0
20	A: 0.889 E-09 D: -0.306 E-21 102.95 (aspherical) K: -0.236	B: 0.557 E-13 E: 0.298 E-25 30.00	C: 0.133 E-17 F: 0 1.560772
21	A: 0.719 E-09 D: -0.752 E-19 318.28	B: -0.318 E-11 E: -0.309 E-22 32.79	C: -0.675 E-15 F: 0 1.0
22	230.0	20.00	1.560772
23	350.93 (aspherical) K: -18.95	33.58	1.0
24	A: 0.107 E-06 D: -0.799 E-16 IMG: INFINITY (IMAGE PLANE)	B: -0.977 E-10 E: 0.340 E-19 -0.0024	C: 0.337 E-13 F: 0

[0069] Figure 13 is a schematic view of an optical system which is to be compared for reference with the projection optical systems according to the numerical examples 1 - 3 above. In Figure 13, diffractive optical elements BOE1 and BOE2 are provided on the surface of one lens, which is on the object side of the aperture stop SP and is far remote from it, and on the surface of another lens which is on the image plane side of the aperture stop SP and is adjacent to it.

[0070] Figures 14 and 15 show aberrations of the reference example of projection optical system shown in Figure 13. It is seen that, although the optical system is provided by a single glass material, aberrations including chromatic aberration are well corrected.

[0071] Figure 16 shows an intensity distribution of unwanted diffraction light upon the image plane, in this reference example, wherein the intensity of unwanted light is illustrated as being standardized with respect to the intensity of diffraction light of design order. Calculation of unwanted diffraction light here is based on that there is a circular opening of a radius 50 mm on the object plane and the luminance distribution and light orientation distribution are uniform over the whole circular opening, and that each of two diffractive optical elements has a step structure of eight levels.

[0072] It is seen from Figure 16 that in this example the intensity ratio of the unwanted diffraction light to the diffraction light of design order is about 3.2% at the center of the picture field, and that, regarding the uniformness of intensity ratio on the image plane, there is a difference of about 1% between the central portion and the peripheral portion. Such intensity ratio and its uniformness are insufficient for a projection exposure apparatus for submicron or quartermicron order lithography.

[0073] Figure 24 shows the relation between the effective radius of the diffractive optical element and the frequency, in the case where the projection optical system shown in Figure 13 is used. Numerical data of the reference example where the projection optical system of Figure 13 is used, will be described below.

[Numerical Data of Reference Example]

[0074] Spec.: Magnification=1/4, NA=0.50 $\lambda=193.00\text{nm}$

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	Surface Number	Curvature Radius	Surface Spacing	Refractivity ($\lambda=193.00\text{nm}$)
5	OBJ	INFINITY	66.934	1.0
	1	-247.81	15.00	1.560772
	2	84.43	81.29	1.0
		(aspherical) K: -2.15		
10		A: 0.476 E-08	B: -0.522 E-11	C: 0.132 E-14
		D: -0.239 E-18	E: 0.277 E-22	F: 0
	3	343.68	35.00	1.560772
		(aspherical) K: -3.248		
15		A: -0.115 E-07	B: 0.722 E-12	C: -0.178 E-17
		D: -0.692 E-20	E: -0.192 E-24	F: 0
	4	-223.10	54.65	1.0
		(aspherical) K: -0.076		
20		A: 0.148 E-08	B: 0.212 E-12	C: -0.449 E-16
		D: -0.149 E-20	E: 0.116 E-23	F: -0.228 E-27
	5	232.87	31.60	1.560772
		(BOE) Design Order -1 $\lambda_p=632.80\text{nm}$		
25		C1: -1.540 E-03	C2: 4.054 E-09	C3: 4.625 E-13
	6	-1003.71	61.93	1.0
	7	322.97	12.00	1.560772
	8	171.11	14.75	1.0
		(aspherical) K: 0.000000		
30		A: -0.184 E-07	B: 0.159 E-10	C: 0.679 E-14
		D: -0.233 E-17	E: 0.637 E-22	F: 0
	9	317.08	12.500	1.560772
	10	176.95	20.88	1.0
		(aspherical) K: -3.802		
35		A: -0.654 E-07	B: -0.655 E-10	C: -0.109 E-13
		D: -0.175 E-17	E: 0.158 E-20	F: 0
	11	-137.87	10.750000	1.560772
		(aspherical) K: 4.32		
40		A: -0.129 E-06	B: -0.104 E-10	C: 0.151 E-13
		D: -0.108 E-16	E: 0.422 E-20	F: 0
	12	145.47	109.56	1.0
		(aspherical) K: -0.0333		
45		A: -0.130 E-08	B: -0.158 E-11	C: -0.375 E-15
		D: 0.308 E-19	E: 0.283 E-22	F: -0.104 E-25
	13	-572.00	45.00	1.560772
		(aspherical) K: 0.117		
50		A: -0.854 E-10	B: -0.114 E-13	C: 0.985 E-18
		D: 0.106 E-21	E: 0.131 E-26	F: -0.257 E-25
	14	-173.10	1.00	1.0
		(aspherical) K: 0.008		
55		A: -0.127 E-09	B: 0.851 E-14	C: -0.242 E-17
		D: -0.961 E-22	E: -0.183 E-27	F: -0.680 E-30
	15	STOP INFINITY (Stop)	32.800000	1.0
	16	718.77	42.19	1.560772

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(continued)

Surface Number	Curvature Radius	Surface Spacing	Refractivity ($\lambda=193.00\text{nm}$)
17	(aspherical) K: -0.261		
	A: 0.453 E-09	B: -0.174 E-13	C: -0.416 E-18
	D: -0.103 E-21	E: 0.591 E-26	F: -0.102 E-30
	-476.54	267.46	1.0
20	(BOE) Design Order -1 λ p=632.80nm		
	C1: 3.164 E-03	C2:-4.434 E-11	C3:-1.147 E-13
	93.29	30.34	1.560772
21	(aspherical) K: -0.200		
	A: 0.174 E-09	B: -0.208 E-12	C: -0.121 E-14
	D: 0.235 E-18	E: -0.507 E-22	F: 0
	163.11	29.87	1.0
22	677.38	16.00	1.560772
	270.97	15.07	1.0
24	78.47	30.00	1.560772
	INFINITY	9.50	1.0
26	(aspherical) K: -0.813		
	A: 0.428 E-07	B: 0.276 E-11	C: -0.387 E-11
	D: 0.108 E-13	E: -0.108 E-16	F: 0
	IMG: INFINITY (IMAGE PLANE)	-0.0024	

[0075] Figure 17 is a schematic view of another optical system which is to be compared for reference with the projection optical systems according to the numerical examples 1 - 3 described above. In Figure 17, diffractive optical elements BOE1 and BOE2 are provided on the surface of one lens, which is on the object side of the aperture stop SP and is adjacent to, and on the surface of another lens which is on the image plane side of the aperture stop SP and is far remote from it.

[0076] Figures 18 and 19 show aberrations of the reference example of projection optical system shown in Figure 17. It is seen that, although the optical system is provided by a single glass material, aberrations including chromatic aberration are well corrected.

[0077] Figure 20 shows an intensity distribution of unwanted diffraction light upon the image plane, in this reference example, wherein the intensity of unwanted light is illustrated as being standardized with respect to the intensity of diffraction light of design order. Calculation of unwanted diffraction light here is based on that there is a circular opening of a radius 50 mm on the object plane and the luminance distribution and light orientation distribution are uniform over the whole circular opening, and that each of two diffractive optical elements has a step structure of eight levels.

[0078] It is seen from Figure 20 that in this example the intensity ratio of the unwanted diffraction light to the diffraction light of design order is about 3% at the center of the picture field, and that, regarding the uniformness of intensity ratio on the image plane, there is a difference of more than about 1.2% between the central portion and the peripheral portion. Such intensity ratio and its uniformness are insufficient for a projection exposure apparatus for submicron or quartermicron order lithography.

[0079] Figure 25 shows the relation between the effective radius of the diffractive optical element and the frequency, in the case where the projection optical system shown in Figure 17 is used. Numerical data of the reference example where the projection optical system of Figure 17 is used, will be described below.

[Numerical Data of Second Reference Example]

[0080] Spec.: Magnification=1/4, NA=0.50 $\lambda=193.00\text{nm}$

Surface Number	Curvature Radius	Surface Spacing	Refractivity ($\lambda=193.00\text{nm}$)
OBJ	INFINITY	148.522	1.0

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(continued)

	Surface Number	Curvature Radius	Surface Spacing	Refractivity ($\lambda=193.00\text{nm}$)
5	1	364.94	15.00	1.560772
	2	144.69	49.105	1.0
		(aspherical) K: -1.67		
		A: 0.269 E-07	B: -0.934 E-12	C: -0.422 E-16
10		D: 0.180 E-19	E: -0.336 E-23	F: 0
	3	310.34	30.00	1.560772
		(aspherical) K: 0.437		
		A: 0.117 E-08	B: -0.222 E-12	C: -0.118 E-16
15		D: 0.143 E-20	E: -0.256 E-24	F: 0
	4	-548.43	58.28	1.0
	5	299.43	30.00	1.560772
	6	-721.07	184.57	1.0
	7	140.06	13.00	1.560772
20	8	125.44	15.00	1.0
		(aspherical) K: 0.000000		
		A: -0.510 E-08	B: 0.208 E-10	C: 0.926 E-14
		D: -0.113 E-17	E: 0.184 E-21	F: 0
25	9	-1018.49	13.00	1.560772
	10	231.49	21.00	1.0
		(aspherical) K: 0.398		
		A: -0.254 E-07	B: -0.734 E-10	C: -0.151 E-13
30		D: -0.259 E-17	E: 0.232 E-20	F: 0
	11	-143.54	13.00	1.560772
		(aspherical) K: 4.85		
		A: -0.140 E-06	B: -0.180 E-10	C: 0.105 E-13
35		D: -0.817 E-17	E: 0.503 E-20	F: 0
	12	127.31	109.09	1.0
	13	-605.58	35.00	1.560772
		(BOE) Design Order -1 $\lambda_p=632.80\text{nm}$		
40		C1 4.471 E-03	C2:-2.739 E-09	C3: 1.234 E-13
	14	-166.85	1.00	1.0
		(aspherical) K: -0.0002		
		A: -0.658 E-09	B: 0.235 E-12	C: 0.704 E-17
		D: 0.186 E-22	E: -0.147 E-26	F: -0.555 E-31
45	15	STOP INFINITY (Stop)	32.00	1.0
	16	322.05	37.00	1.560772
		(aspherical) K: 0.6368		
		A: 0.112 E-08	B: -0.551 E-13	C: 0.271 E-17
50		D: 0.104 E-21	E: -0.287 E-25	F: -0.102 E-30
	17	-1103.52	126.01	1.0
		(aspherical) K: -0.533		
		A: 0.618 E-10	B: -0.200 E-14	C: 0.234 E-18
55		D: 0.569 E-22	E: 0.664 E-26	F: -0.834 E-31
	18	114.88	30.00	1.560772
		(aspherical) K: -0.271		

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(continued)

Surface Number	Curvature Radius	Surface Spacing	Refractivity ($\lambda=193.00\text{nm}$)
19	A: -0.824 E-08	B: -0.830 E-13	C: -0.75 E-17
	D: -0.889 E-20	E: -0.200 E-22	F: 0
	514.74	36.12	1.0
	(aspherical) K: 9.51		
20	A: 0.122 E-07	B: 0.268 E-11	C: 0.903 E-16
	D: -0.130 E-18	E: -0.241 E-22	F: 0
	687.47	18.00	1.560772
21	-555.18	16.74	1.0
	(BOE) Design Order -1 λ p=632.80nm		
22	C1: 1.542 E-03	C2: 1.224 E-08	C3: -9.748 E-12
	-287.19	20.00	1.560772
	-1580.54	18.88	1.0
	(aspherical) K: -120.54		
24	A: 0.155 E-06	B: -0.454 E-09	C: 0.480 E-12
	D: -0.672 E-15	E: 0.400 E-18	F: 0
	IMG: INFINITY (IMAGE PLANE)	-0.0024	

[0081] Next, the relation between the condition equations (1) and (2) or (1') and (2') and the numerical examples 1, 2 and 3, described above, will be explained.

TABLE 1

CONDITIONS		NUMERICAL EXAMPLES		
		#1	#2	#3
(1) d/D	d_1/D	0.04	0.07	0.08
	d_2/D	0.07	0.11	0.05
(2) h/H	h_1/H	0.94	1.09	0.91
	h_2/h	1.01	1.00	1.01

[0082] Although the foregoing embodiments have been described with reference to a projection exposure apparatus for manufacture of semiconductor devices, the present invention is similarly applicable also to any other optical instruments where unwanted diffraction light from a diffractive optical element reaches an image plane to produce undesirable effect such as non-uniformness of exposure, for example.

[0083] Next, an embodiment of device manufacturing method which uses a projection exposure apparatus as described above, will be explained.

[0084] Figure 28 is a flow chart of procedure for manufacture of microdevices such as semiconductor chips (e.g. ICs or LSIs), liquid crystal panels, or CCDs, for example.

[0085] Step 1 is a design process for designing a circuit of a semiconductor device. Step 2 is a process for making a mask on the basis of the circuit pattern design. Step 3 is a process for preparing a wafer by using a material such as silicon. Step 4 is a wafer process which is called a pre-process wherein, by using the so prepared mask and wafer, circuits are practically formed on the wafer through lithography. Step 5 subsequent to this is an assembling step which is called a post-process wherein the wafer having been processed by step 4 is formed into semiconductor chips. This step includes assembling (dicing and bonding) process and packaging (chip sealing) process. Step 6 is an inspection step wherein operation check, durability check and so on for the semiconductor devices provided by step 5, are carried out. With these processes, semiconductor devices are completed and they are shipped (step 7).

[0086] Figure 29 is a flow chart showing details of the wafer process. Step 11 is an oxidation process for oxidizing the surface of a wafer. Step 12 is a CVD process for forming an insulating film on the wafer surface. Step 13 is an electrode forming process for forming electrodes upon the wafer by vapor deposition. Step 14 is an ion implanting process for implanting ions to the wafer. Step 15 is a resist process for applying a resist (photosensitive material) to the wafer. Step 16 is an exposure process for printing, by exposure, the circuit pattern of the mask on the wafer through

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the exposure apparatus described above. Step 17 is a developing process for developing the exposed wafer. Step 18 is an etching process for removing portions other than the developed resist image. Step 19 is a resist separation process for separating the resist material remaining on the wafer after being subjected to the etching process. By repeating these processes, circuit patterns are superposedly formed on the wafer.

[0087] With these processes, high density microdevices can be manufactured.

[0088] While the invention has been described with reference to the structures disclosed herein, it is not confined to the details set forth and this application is intended to cover such modifications or changes as may come within the scope of the following claims.

Claims

1. A projection exposure apparatus, comprising:

an illumination optical system for illuminating a mask (M) with light from a light source (ED); and
a projection optical system (PL) having at least one diffractive optical element (BOE1, BOE2), for projecting an image of a pattern of the illuminated mask (M) onto a substrate (W), wherein said at least one diffractive optical element (BOE1, BOE2) is adapted to produce first diffraction light of a first predetermined diffraction order for projecting the image, and second diffraction light of a diffraction order different from that of the first diffraction light,

characterised in that an intensity distribution upon the substrate (W) of that portion of the second diffraction light to be superimposed on the image of the pattern upon the substrate (W) is substantially uniform.

2. An apparatus according to claim 1, wherein one portion of the second diffraction light is not projected onto the substrate (W), while the remaining portion of the second diffraction light is projected onto the substrate (W) to produce a uniform intensity distribution on the substrate (W).

3. An apparatus according to claim 2, wherein said one portion of the second diffraction light is projected onto an inside wall of a lens barrel for supporting said projection optical system while another portion is projected onto the substrate (W).

4. An apparatus according to any preceding claim, wherein said diffractive optical element is disposed at or adjacent the position of an aperture stop (SP) of said projection optical system.

5. An apparatus according to any of claims 1 to 4, wherein, when the distance between the mask (M) and the substrate (W) is D, the distance from the position of the aperture stop (SP) to the position of said diffractive optical element (BOE1, BOE2) is d, and the height of a maximum light ray at the aperture stop (SP) position that determines the numerical aperture of said projection optical system and the incidence height thereof to said diffractive optical element are H and h, respectively, the following relations are satisfied:

$$0.005 < d/D < 0.12$$

$$0.8 < h/H < 1.2$$

6. An apparatus according to claim 4, wherein said projection optical system includes at least two diffractive optical elements (BOE1, BOE2) disposed at or adjacent the position of an aperture stop (SP) of said projection optical system, and wherein said at least two diffractive optical elements (BOE1, BOE2) are adapted to produce the first and second diffraction lights.

7. An apparatus according to claim 6, wherein said projection optical system includes first and second diffractive optical elements (BOE1, BOE2) and an aperture stop (SP), and wherein the first and second diffractive optical elements are disposed on opposite sides of the aperture stop (SP).

8. An apparatus according to claim 6, wherein said projection optical system includes first and second diffractive optical elements (BOE1, BOE2) and an aperture stop (SP), and wherein the first and second diffractive optical

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elements are positioned between the mask (M) and the aperture stop (SP).

9. An apparatus according to claim 6, wherein said projection optical system includes first and second diffractive optical elements (BOE1, BOE2) and an aperture stop (SP), and wherein the first and second diffractive optical elements are positioned between the substrate (W) and the aperture stop (SP).

10. An apparatus according to any of claims 6 to 9, wherein, when the distance between the mask (M) and the substrate (W) is D, the distance from the position of the aperture stop (SP) to the position of an i-th diffractive optical element is d_i , wherein i is an integer, and the height of a maximum light ray at the aperture stop (SP) position that determines the numerical aperture of said projection optical system and the incidence height thereof to said diffractive optical element (BOE1, BOE2) are H and h_i , respectively, the following relations are satisfied:

$$0.005 < d_i/D < 0.12$$

$$0.8 < h_i/H < 1.2$$

11. An apparatus according to any preceding claim, wherein said projection optical system further includes an aspherical surface lens.

12. An apparatus according to any preceding claim, wherein said at least one diffractive optical element (BOE1, BOE2) is adapted to correct axial chromatic aberration of said projection optical system as well as colour coma aberration.

13. An apparatus according to any of claims 6 to 9, wherein there are two diffractive optical elements (BOE1, BOE2) and said two diffractive optical elements have respective frequencies fR_1 and fR_2 and wherein at the largest effective diameter of the optical elements the respective frequencies satisfy the following relation:

$$fR_1/fR_2 < 2.5.$$

14. An apparatus according to any preceding claim, wherein the light source comprises a KrF excimer laser, ArF excimer laser or an F_2 laser.

15. An apparatus according to any preceding claim, wherein said projection optical system uses a glass material of quartz only.

16. An apparatus according to any of claims 1 to 14, wherein said projection optical system uses glass materials of quartz and fluorite only.

17. An apparatus according to any preceding claim wherein the image of the pattern contains a line whose width is not greater than 0.25 mm.

18. An apparatus according to any preceding claim, adapted to project the image of the pattern sequentially onto different portions of the substrate (W) through a step-and-repeat process.

19. An apparatus according to any of claims 1 to 17, adapted to project the image of the pattern sequentially onto different portions of the substrate (W) through a step-and-scan process.

20. A device manufacturing method comprising the steps of:

projecting a pattern of a reticle (M) onto a wafer (W) by use of a projection exposure apparatus according to any preceding claim;
performing a development process on the exposed wafer; and
manufacturing a device from the exposed and developed wafer.

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Patentansprüche

1. Projektionsbelichtungsgerät, das umfasst:

5 ein optisches Beleuchtungssystem zum Beleuchten einer Maske (M) mit Licht aus einer Lichtquelle (ED); und ein optisches Projektionssystem (PL) mit wenigstens einem optischen Beugungselement (BOE1, BOE2) zum Projizieren eines Bildes mit einem Muster der beleuchteten Maske (M) auf ein Substrat (W), wobei das wenigstens eine optische Beugungselement (BOE1, BOE2) angepasst ist, um ein erstes Beugungslicht einer ersten vorbestimmten Beugungsordnung zum Projizieren des Bildes, und ein zweites Beugungslicht einer

10 Beugungsordnung, das von demjenigen des ersten Beugungslichtes verschieden ist, herzustellen, **dadurch gekennzeichnet, dass** eine Intensitätsverteilung bei dem Substrat (W) von dem Teil des zweiten Beugungslichtes, das auf dem Bild des Musters bei dem Substrat (W) überlagert wird, im Wesentlichen gleichförmig ist.

15 2. Gerät gemäß Anspruch 1, wobei ein Teil des zweiten Beugungslichtes nicht auf das Substrat (W) projiziert wird, während der verbleibende Teil des zweiten Beugungslichtes auf das Substrat (W) projiziert wird, um eine gleichförmige Intensitätsverteilung auf dem Substrat (W) herzustellen.

20 3. Gerät gemäß Anspruch 2, wobei der eine Teil des zweiten Beugungslichtes auf eine innere Wand eines Objektivtubus projiziert wird, um das optische Projektionssystem zu unterstützen, während ein anderer Teil auf das Substrat (W) projiziert wird.

4. Gerät gemäß einem der vorhergehenden Ansprüche, wobei das optische Beugungselement bei oder nahe der Position eines Aperturstopps (SP) des optischen Projektionssystem angeordnet ist.

25 5. Gerät gemäß einem der Ansprüche 1 bis 4, wobei, wenn der Abstand zwischen der Maske (M) und dem Substrat (W) D ist, der Abstand von der Position des Aperturstopps (SP) zu der Position des optischen Beugungselementes (BOE1, BOE2) d ist, und die Höhe eines maximalen Lichtstrahls bei der Aperturstopp (SP) Position, die die numerische Apertur des optischen Projektionssystem und deren Einfallhöhe auf das optische Beugungselement bestimmt, jeweils H und h sind, wobei die folgenden Beziehungen erfüllt sind:

$$0,005 < d/D < 0,12$$

35 $a \cdot 0,8 < h/H < 1,2$

6. Gerät gemäß Anspruch 4, wobei das optische Projektionssystem wenigstens 2 optische Beugungselemente (BOE1, BOE2) beinhaltet, die bei oder nahe der Position eines Aperturstopps (SP) des optischen Projektionssystem angeordnet sind, und wobei die wenigstens zwei optischen Beugungselemente (BOE1, BOE2) angepasst sind, um die ersten und zweiten Beugungslichter herzustellen.

40

7. Gerät gemäß Anspruch 6, wobei das optische Projektionssystem erste und zweite optische Beugungselemente (BOE1, BOE2) und einen Aperturstopp (SP) beinhaltet, und wobei die ersten und zweiten optischen Beugungselemente auf entgegengesetzten Seiten des Aperturstopps (SP) angeordnet sind.

45

8. Gerät gemäß Anspruch 6, wobei das optische Projektionssystem erste und zweite optische Beugungselemente (BOE1, BOE2) und einen Aperturstopp (SP) beinhaltet, und wobei die ersten und zweiten optischen Beugungselemente zwischen der Maske (M) und dem Aperturstopp (SP) positioniert sind.

50 9. Gerät gemäß Anspruch 6, wobei das optische Projektionssystem erste und zweite optische Beugungselemente (BOE1, BOE2) und einen Aperturstopp (SP) beinhaltet, und wobei die ersten und zweiten optischen Beugungselemente zwischen dem Substrat (W) und dem Aperturstopp (SP) positioniert sind.

55 10. Gerät gemäß einem der Ansprüche 1 bis 9, wobei, wenn der Abstand zwischen der Maske (M) und dem Substrat (W) D ist, der Abstand von der Position des Aperturstopps (SP) zu der Position eines i-ten optischen Beugungselementes d_i ist, wobei i eine ganze Zahl ist, und die Höhe eines maximalen Lichtstrahls an der Aperturstopp (SP) -Position, die die numerische Apertur des optischen Projektionssystem deren Einfallhöhe auf das optische Beugungselement (BOE1, BOE2) bestimmt, jeweils H und h_i sind, wobei die folgenden Beziehungen erfüllt sind:

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$$0,005 < d_i/D < 0,12$$

$$0,8 < h_i/H < 1,2$$

5

11. Gerät gemäß einem vorhergehenden Anspruch, wobei das optische Projektionssystem ferner eine aspherische Oberflächenlinse beinhaltet.

10

12. Gerät gemäß einem vorhergehenden Anspruch, wobei das wenigstens eine optische Beugungselement (BOE1, BOE2) angepasst ist, um die axiale chromatische Aberration des optischen Projektionssystems genauso wie die Farbkoma-Aberration zu korrigieren.

15

13. Gerät gemäß einem der Ansprüche 6 bis 9, wobei es zwei optische Beugungselemente (BOE1, BOE2) gibt und die zwei optischen Beugungselemente jeweilige Frequenzen fR_1 und fR_2 aufweisen und wobei an dem größten effektiven Durchmesser der optischen Elemente die jeweiligen Frequenzen die folgende Beziehungen erfüllen:

$$fR_1/fR_2 < 2,5.$$

20

14. Gerät gemäß einem vorhergehenden Anspruch, wobei die Lichtquelle einen KrF-Excimerlaser, ArF-Excimerlaser oder F₂-Laser umfasst.

25

15. Gerät gemäß einem vorhergehenden Anspruch, wobei das optische Projektionssystem ein Glasmaterial aus Quarz allein verwendet.

16. Gerät gemäß einem der Ansprüche 1 bis 14, wobei das optische Projektionssystem Glasmaterialien aus Quarz und Fluorit allein verwendet.

30

17. Gerät gemäß einem vorhergehenden Anspruch, wobei das Bild des Musters eine Linie enthält, dessen Breite nicht größer als 0,25 mm ist.

18. Gerät gemäß einem vorhergehenden Anspruch, das angepasst ist, um das Bild des Musters sequentiell auf verschiedene Teile des Substrats (W) durch ein Schrittlund Wiederholungsverfahren zu projizieren.

35

19. Gerät gemäß einem der Ansprüche 1 bis 17, das angepasst ist, um das Bild des Musters sequentiell auf verschiedene Teile des Substrats (W) durch ein Schrittlund Abtastverfahren zu projizieren.

20. Vorrichtungsherstellungsverfahren, das die folgenden Schritte umfasst:

40

Projizieren eines Musters einer Strichplatte (M) auf einem Wafer (W) unter Verwendung eines Projektionsbelichtungsgeräts einem vorhergehenden Anspruch;
Durchführen eines Entwicklungsverfahrens auf dem belichteten Wafer;
Herstellen einer Vorrichtung aus dem belichteten und entwickelten Wafer.

45

Revendications

1. Dispositif d'exposition de projection, comprenant :

50

un système optique d'éclairage pour éclairer un masque (M) avec une lumière venant d'une source de lumière (ED) ; et

55

un système optique de projection (PL) comprenant au moins un élément optique à diffraction (BOE1, BOE2), pour projeter une image d'un motif du masque éclairé (M) sur un substrat (W), dans lequel ledit élément optique à diffraction au nombre d'au moins un (BOE1, BOE2) est adapté pour produire une première lumière de diffraction d'un premier ordre de diffraction prédéterminé pour projeter l'image, et une deuxième lumière de diffraction d'un ordre de diffraction différent de celui de la première lumière de diffraction,

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caractérisé en ce qu'une distribution d'intensité sur le substrat (W) de la partie de la deuxième lumière de diffraction devant être superposée sur l'image du motif sur le substrat (W) est sensiblement uniforme.

2. Dispositif selon la revendication 1, dans lequel une partie de la deuxième lumière de diffraction n'est pas projetée sur le substrat (W), tandis que la partie restante de la deuxième lumière de diffraction est projetée sur le substrat (W) de façon à produire une distribution d'intensité uniforme sur le substrat (W).
3. Dispositif selon la revendication 2, dans lequel ladite première partie de la deuxième lumière de diffraction est projetée sur une paroi intérieure d'un fût de lentille pour supporter ledit système optique de projection, tandis qu'une autre partie est projetée sur le substrat (W).
4. Dispositif selon l'une quelconque des revendications précédentes, dans lequel ledit élément optique à diffraction est disposé dans la position d'un arrêt d'ouverture (SP) dudit système optique de projection ou au voisinage de celle-ci.
5. Dispositif selon l'une quelconque des revendications 1 à 4, dans lequel, lorsque la distance entre le masque (M) et le substrat (W) est de D, que la distance de la position de l'arrêt d'ouverture (SP) à la position dudit élément optique à diffraction (BOE1, BOE2) est de d, et que la hauteur d'un rayon de lumière maximal dans la position d'arrêt d'ouverture (SP) qui détermine l'ouverture numérique dudit système optique de projection et la hauteur d'incidence de celui-ci par rapport audit élément optique à diffraction sont de H et de h, respectivement, les relations suivantes sont satisfaites :

$$0,005 < d/D < 0,12$$

et

$$0,8 < h/H < 1,2$$

6. Dispositif selon la revendication 4, dans lequel ledit système optique de projection comprend au moins deux éléments optiques à diffraction (BOE1, BOE2) disposés dans la position d'un arrêt d'ouverture (SP) dudit système optique de projection ou au voisinage de celle-ci, et dans lequel lesdits éléments optiques à diffraction au nombre d'au moins deux (BOE1, BOE2) sont adaptés pour produire les première et deuxième lumières de diffraction.
7. Dispositif selon la revendication 6, dans lequel ledit système optique de projection comprend des premier et deuxième éléments optiques à diffraction (BOE1, BOE2) et un arrêt d'ouverture (SP), et dans lequel les premier et deuxième éléments optiques à diffraction sont disposés sur les cotés opposés de l'arrêt d'ouverture (SP).
8. Dispositif selon la revendication 6, dans lequel ledit système optique de projection comprend des premier et deuxième éléments optiques à diffraction (BOE1, BOE2) et un arrêt d'ouverture (SP), et dans lequel les premier et deuxième éléments optiques à diffraction sont positionnés entre le masque (M) et l'arrêt d'ouverture (SP).
9. Dispositif selon la revendication 6, dans lequel ledit système optique de projection comprend des premier et deuxième éléments optiques à diffraction (BOE1, BOE2) et un arrêt d'ouverture (SP), et dans lequel les premier et deuxième éléments optiques à diffraction sont positionnés entre le substrat (W) et l'arrêt d'ouverture (SP).
10. Dispositif selon l'une quelconque des revendications 6 à 9, dans lequel, lorsque la distance entre le masque (M) et le substrat (W) est de D, que la distance de la position de l'arrêt d'ouverture (SP) à la position d'un i^{ème} élément optique à diffraction est de d_i, i étant un entier, et que la hauteur d'un rayon de lumière maximal dans la position d'arrêt d'ouverture (SP) qui détermine l'ouverture numérique dudit système optique de projection et la hauteur d'incidence de celui-ci par rapport audit élément optique à diffraction (BOE1, BOE2) sont de H et de h_i, respectivement, les relations suivantes sont satisfaites :

$$0,005 < d_i/D < 0,12$$

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$$0,8 < h_i/H < 1,2$$

- 5 11. Dispositif selon l'une quelconque des revendications précédentes, dans lequel ledit système optique de projection comprend de plus une lentille à surface asphérique.
- 10 12. Dispositif selon l'une quelconque des revendications précédentes, dans lequel ledit élément optique à diffraction au nombre d'au moins un (BOE1, BOE2) est adapté pour corriger l'aberration chromatique axiale dudit système optique de projection, ainsi que l'aberration de coma de couleur.
- 15 13. Dispositif selon l'une quelconque des revendications 6 à 9, dans lequel il y a deux éléments optiques à diffraction (BOE1, BOE2) et lesdits deux éléments optiques à diffraction ont des fréquences respectives de fR_1 et de fR_2 , et dans lequel, pour le plus grand diamètre efficace des éléments optiques, les fréquences respectives satisfont à la relation suivante :
- $$fR_1/fR_2 < 2,5.$$
- 20 14. Dispositif selon l'une quelconque des revendications précédentes, dans lequel la source de lumière comprend un laser à excimère au KrF, un laser à excimère au ArF ou un laser au F₂.
- 25 15. Dispositif selon l'une quelconque des revendications précédentes, dans lequel ledit système optique de projection utilise un matériau de verre en quartz uniquement.
- 30 16. Dispositif selon l'une quelconque des revendications 1 à 14, dans lequel ledit système optique de projection utilise des matériaux de verre en quartz et en spath fluor uniquement.
- 35 17. Dispositif selon l'une quelconque des revendications précédentes, dans lequel l'image du motif contient une ligne dont la largeur n'est pas supérieure à 0,25 mm.
18. Dispositif selon l'une quelconque des revendications précédentes, adapté pour projeter l'image du motif en séquence sur différentes parties du substrat (W) à l'aide d'un processus par pas et répétition.
19. Dispositif selon l'une quelconque des revendications 1 à 17, adapté pour projeter l'image du motif en séquence sur différentes parties du substrat (W) à l'aide d'un processus par pas et balayage.
20. Procédé de fabrication de dispositif comprenant les étapes suivantes :
- 40 la projection d'un motif d'un réticule (M) sur une plaquette (W) à l'aide d'un dispositif d'exposition de projection selon l'une quelconque des revendications précédentes ;
la réalisation d'un processus de développement sur la plaquette exposée ; et
la fabrication d'un dispositif à partir de la plaquette exposée et développée.
- 45
- 50
- 55

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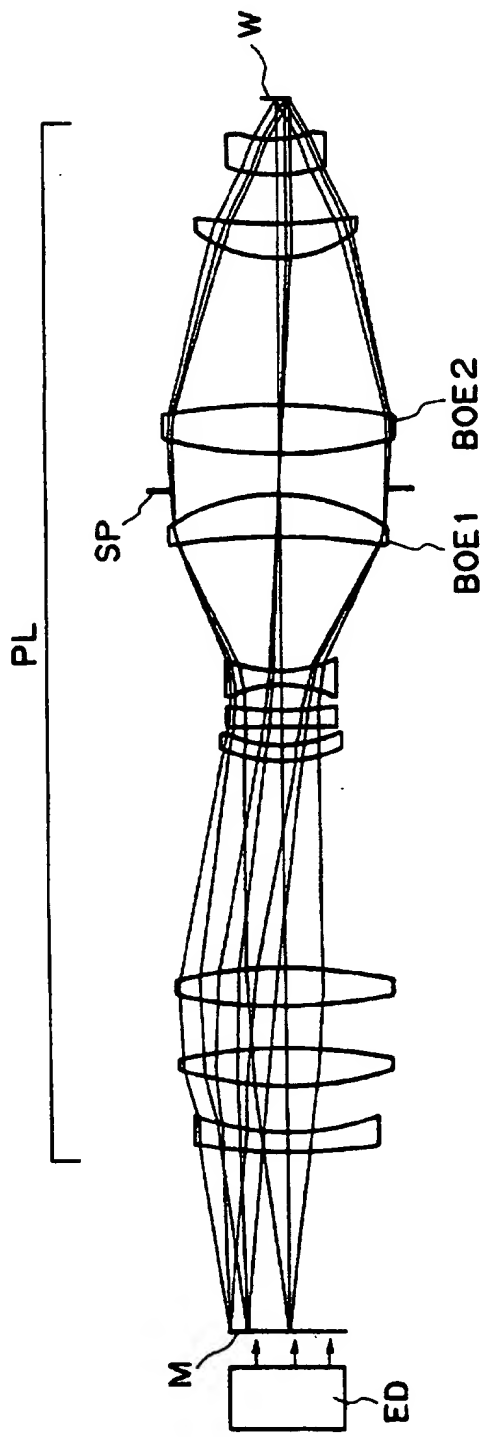


FIG. 1

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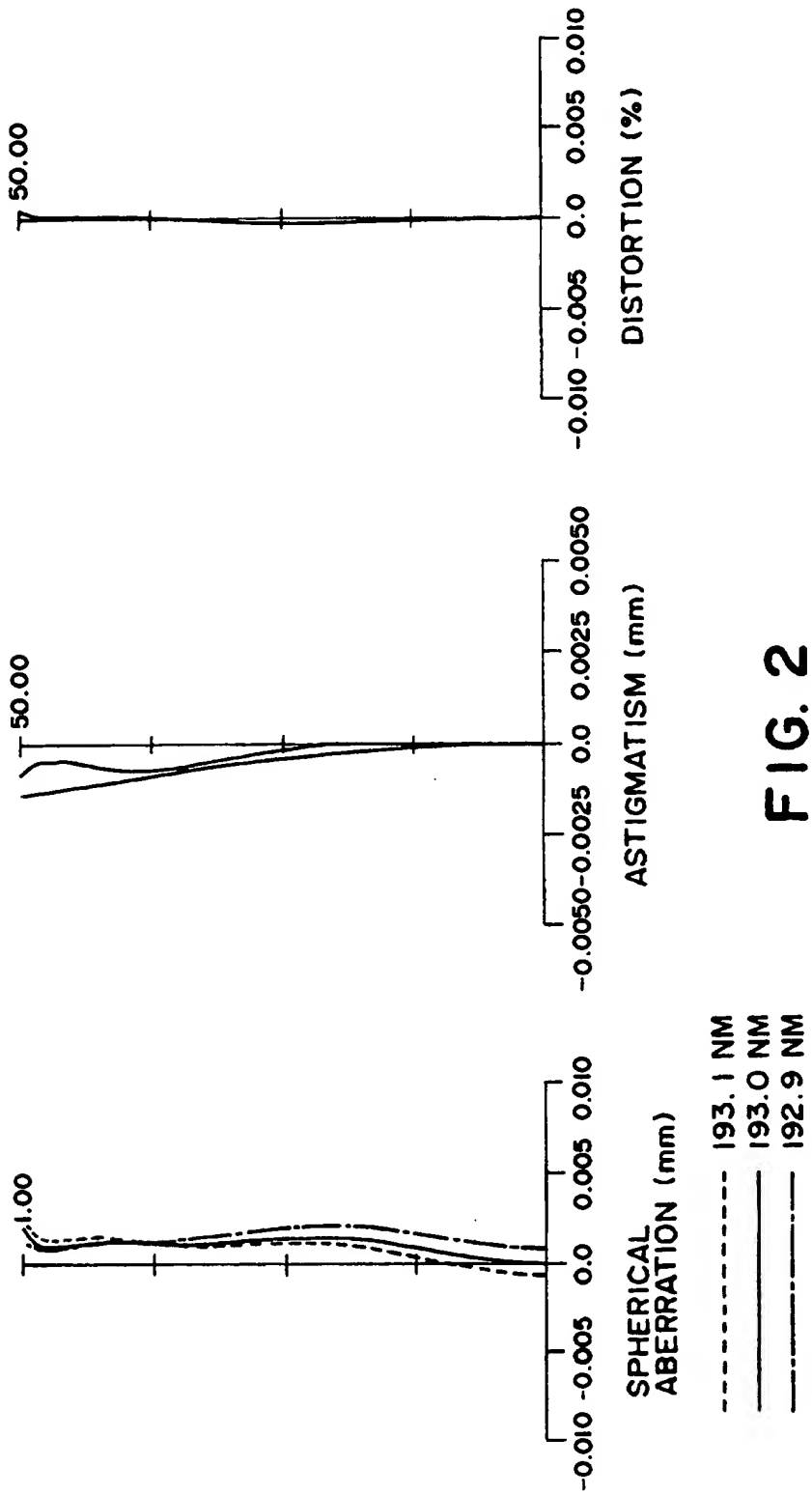


FIG. 2

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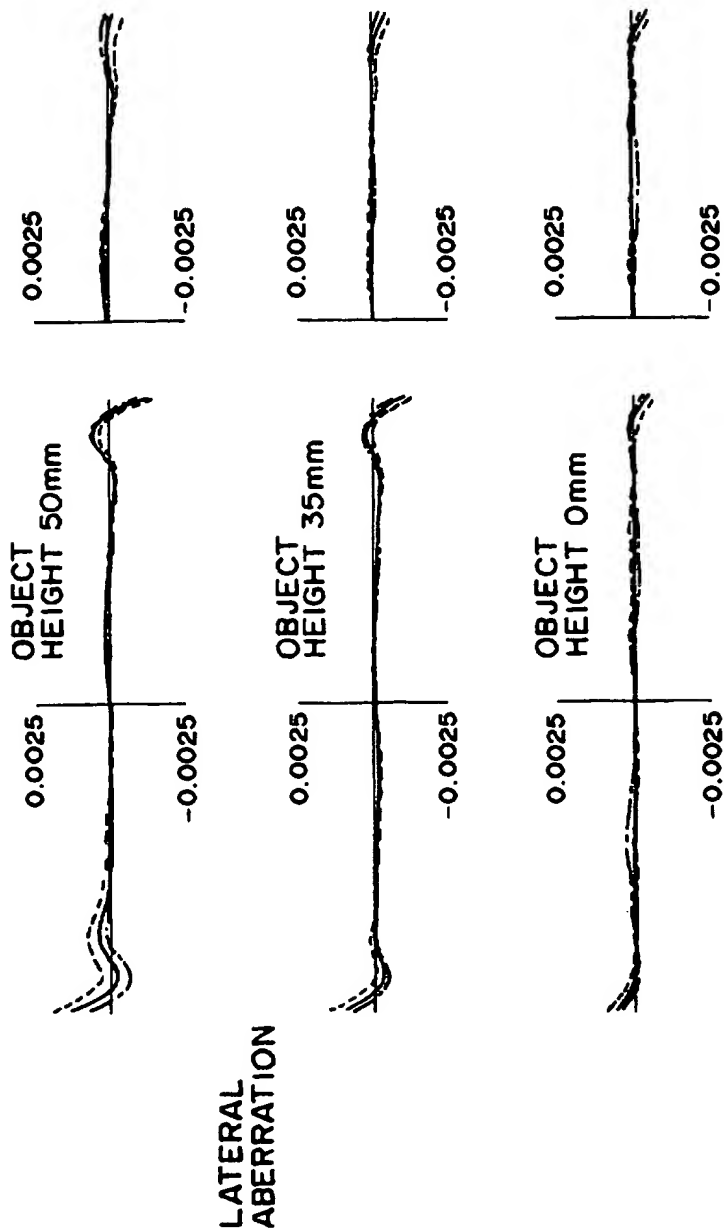


FIG. 3

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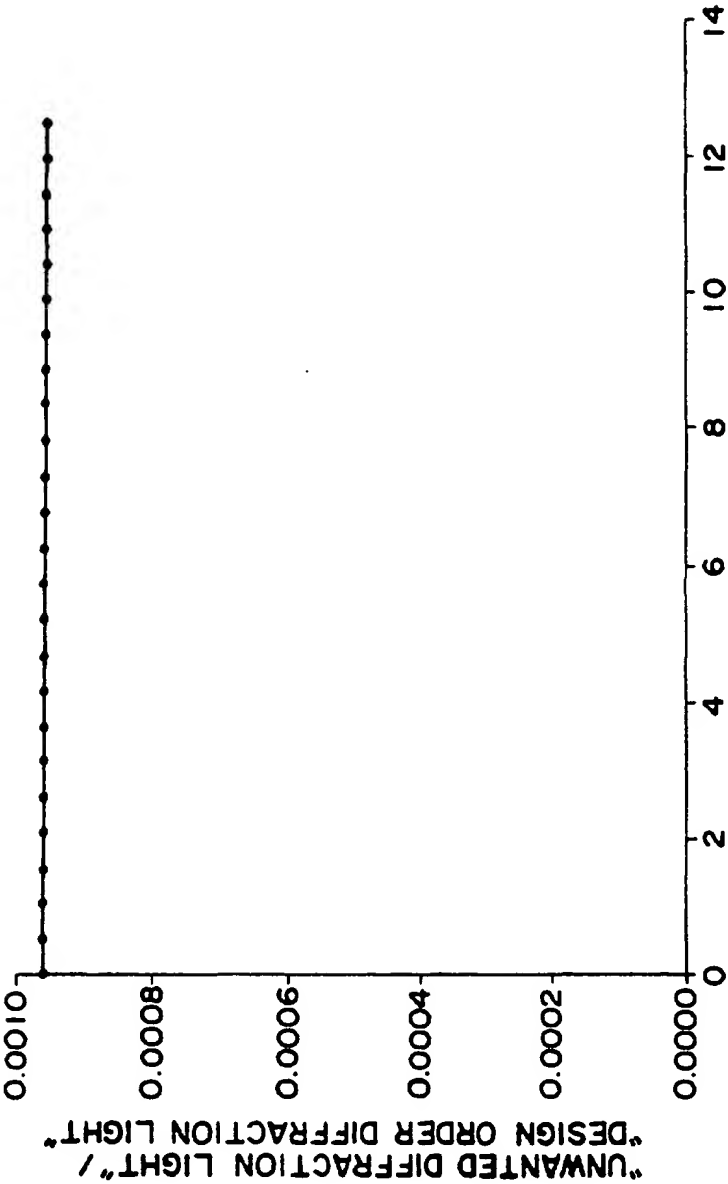


FIG. 4

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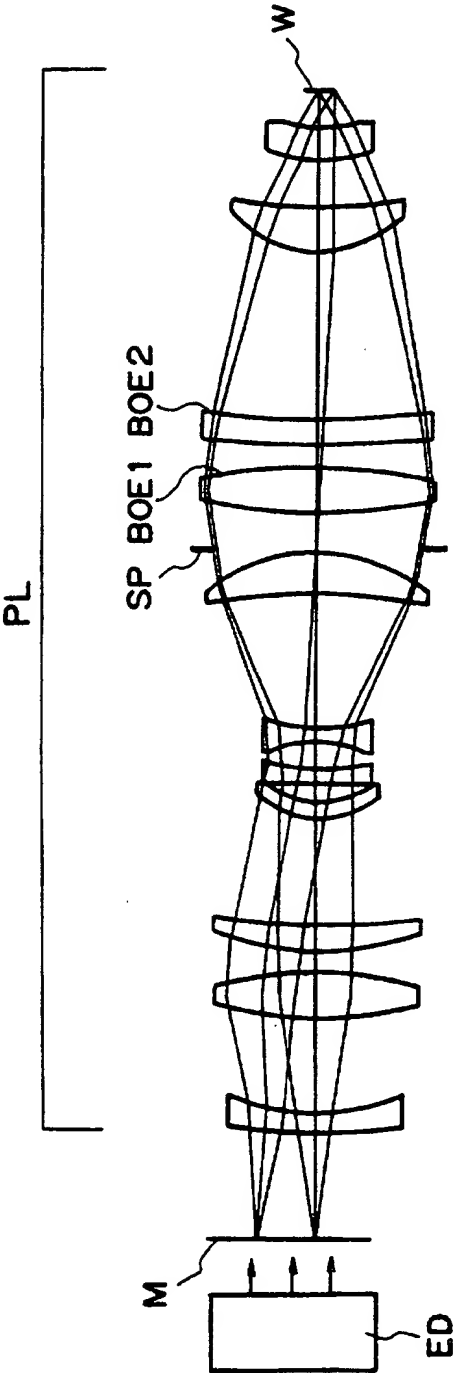
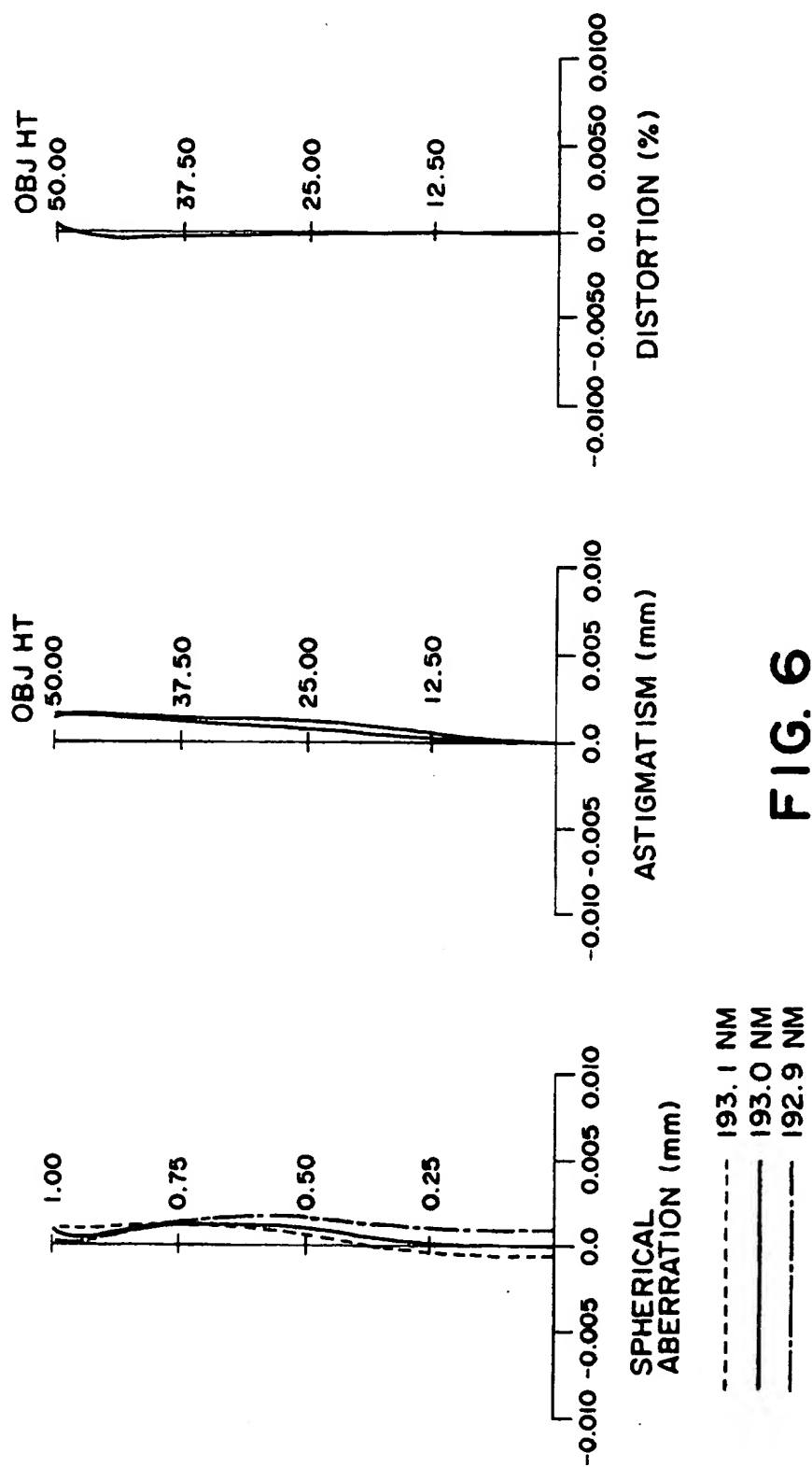


FIG. 5

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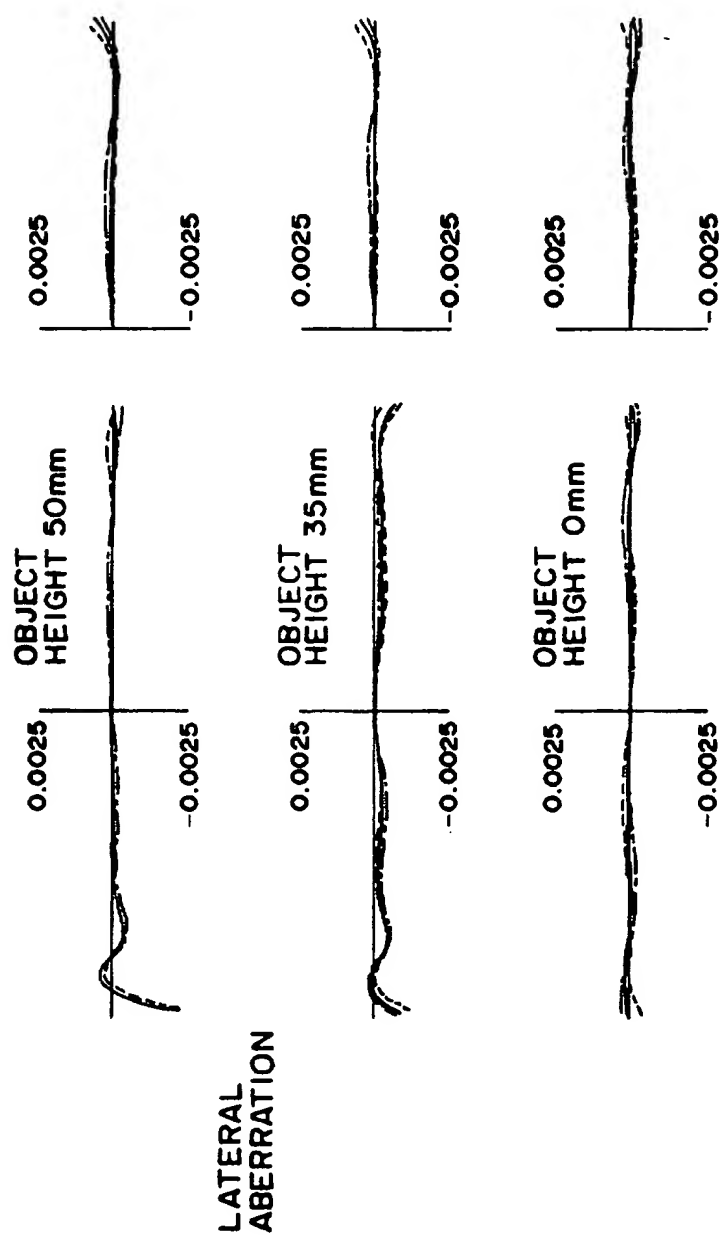


FIG. 7

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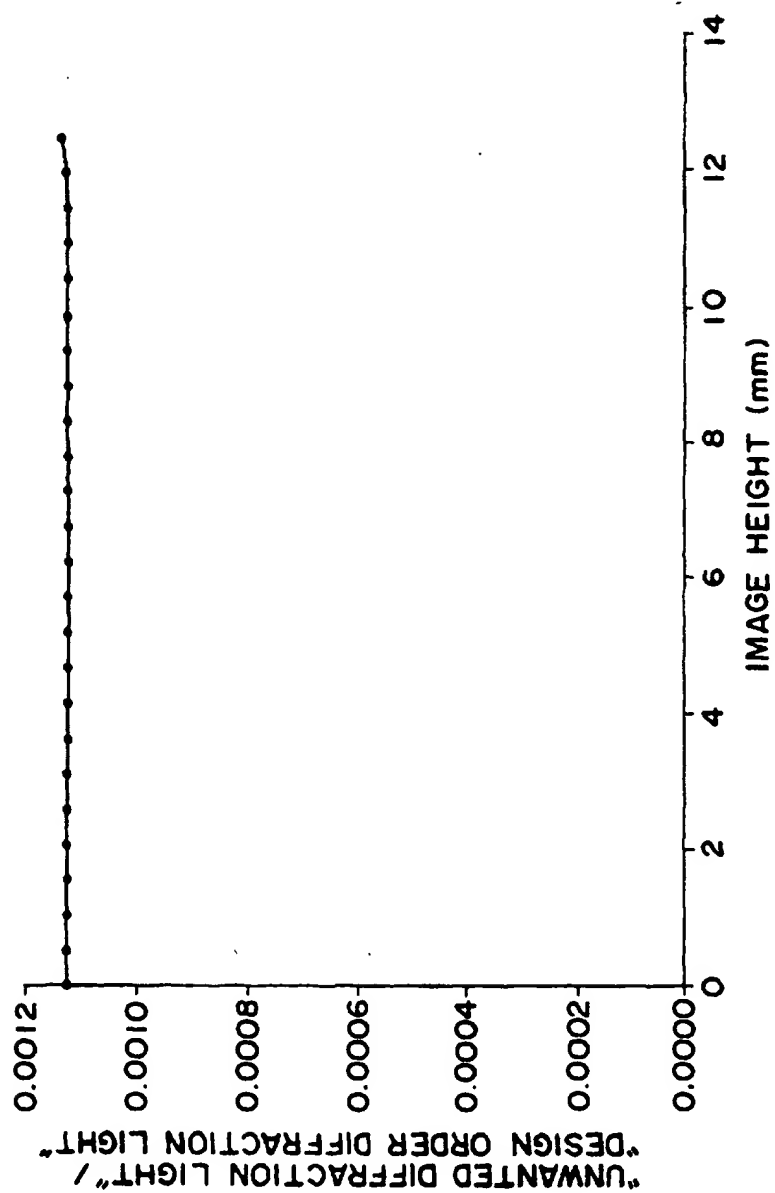


FIG. 8

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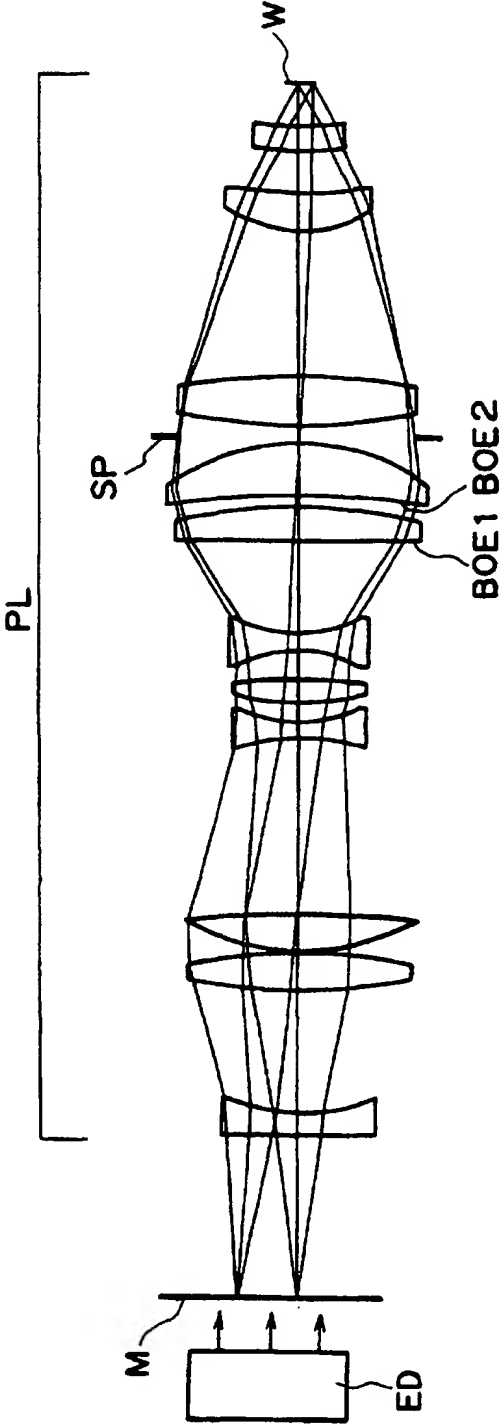
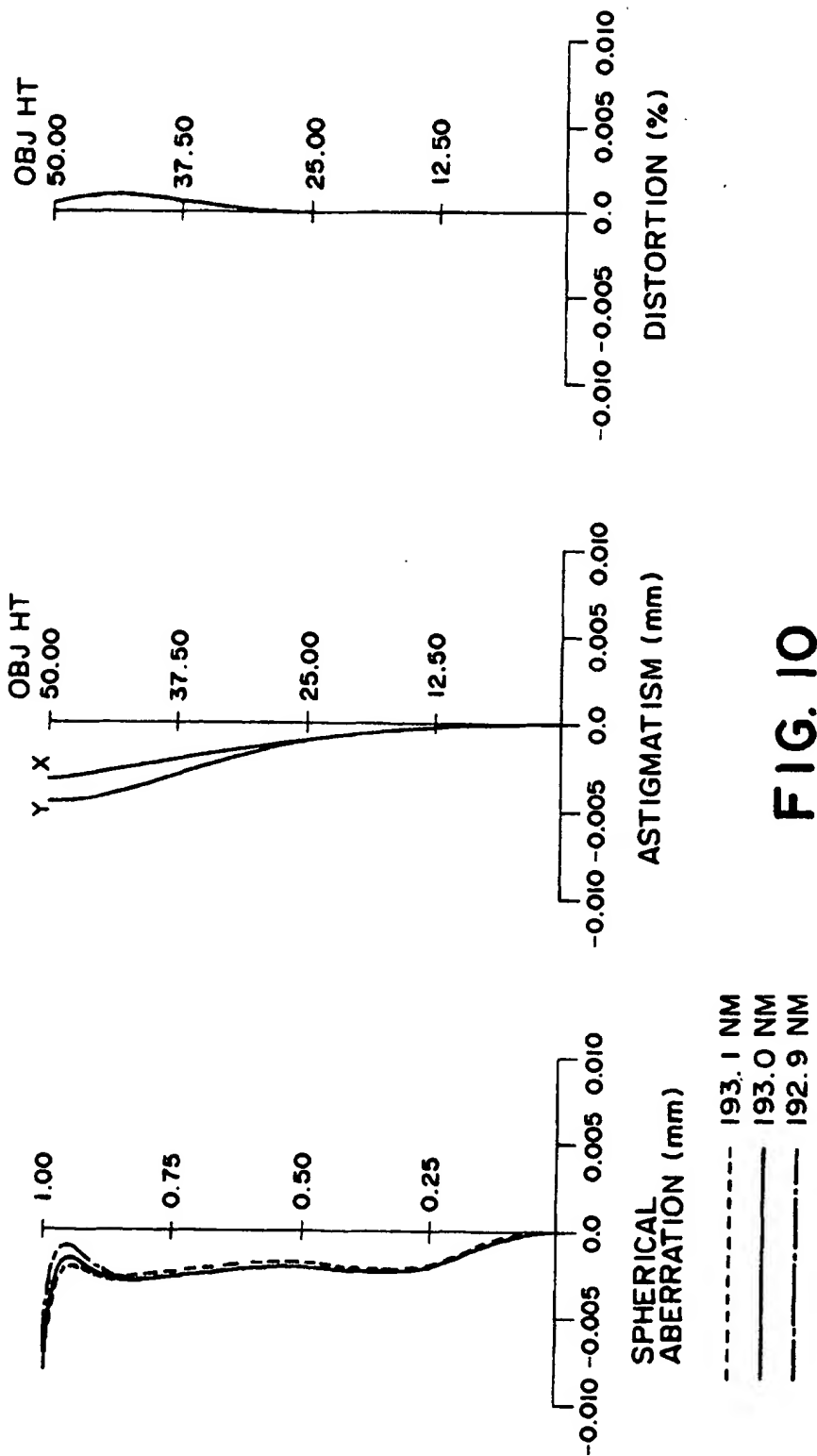


FIG. 9

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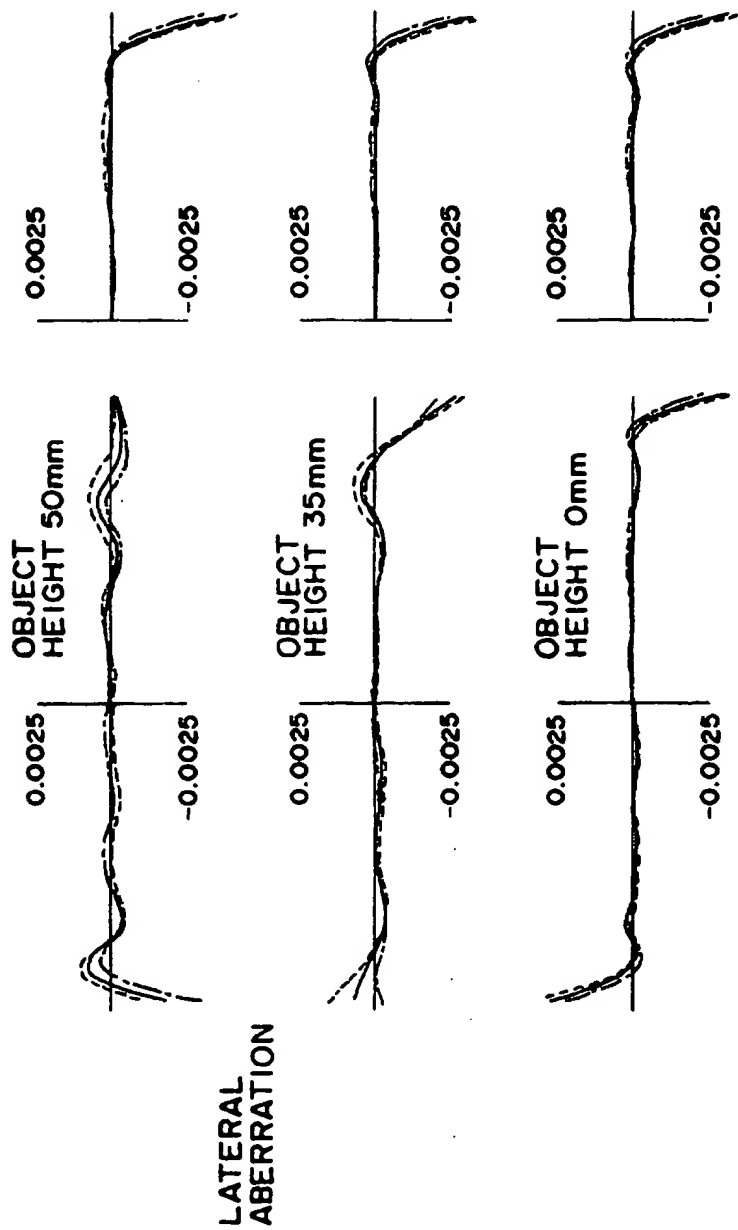


FIG. 11

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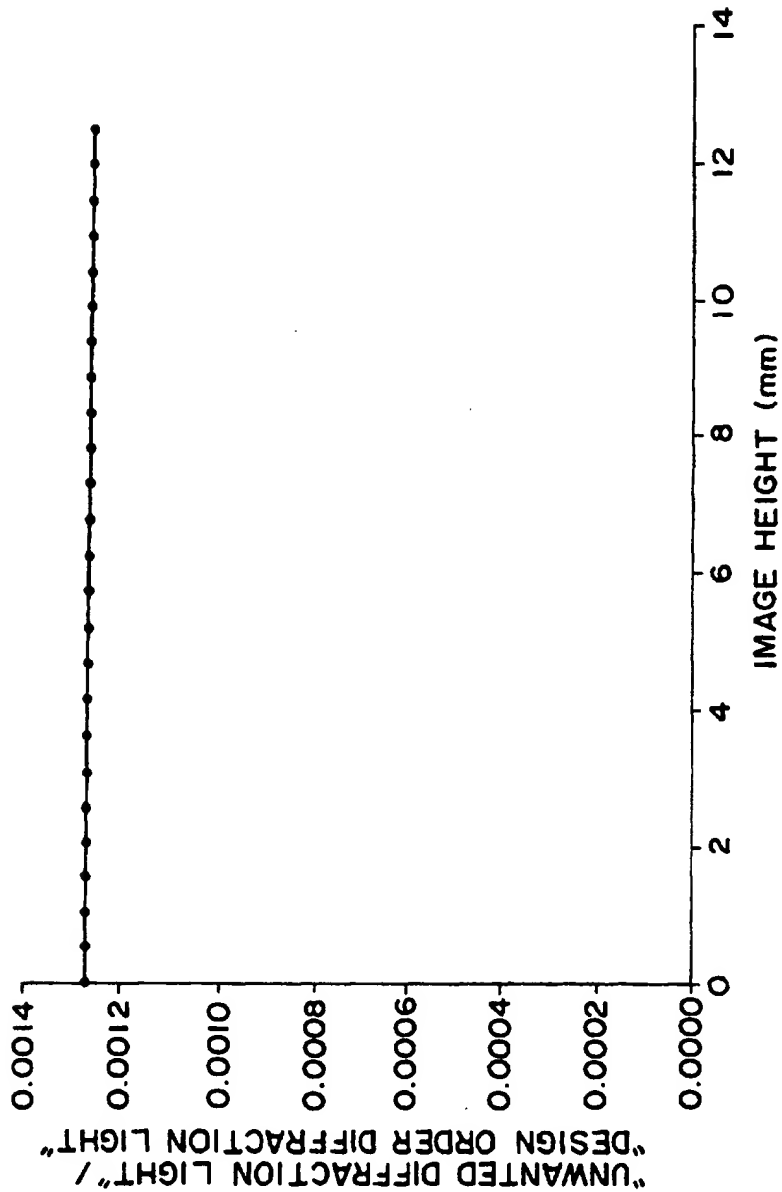


FIG. 12

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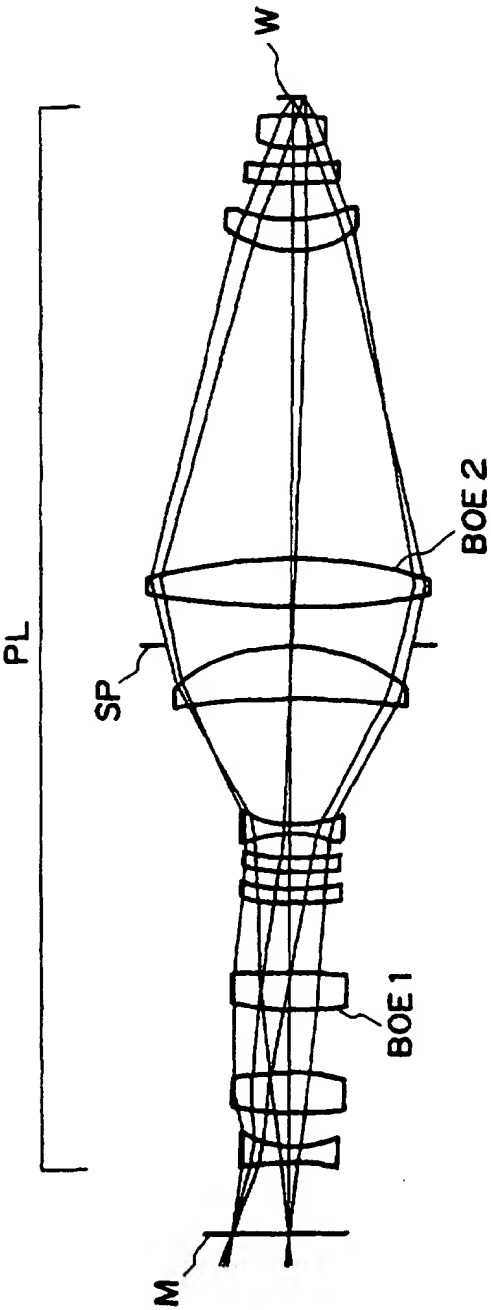


FIG. 13

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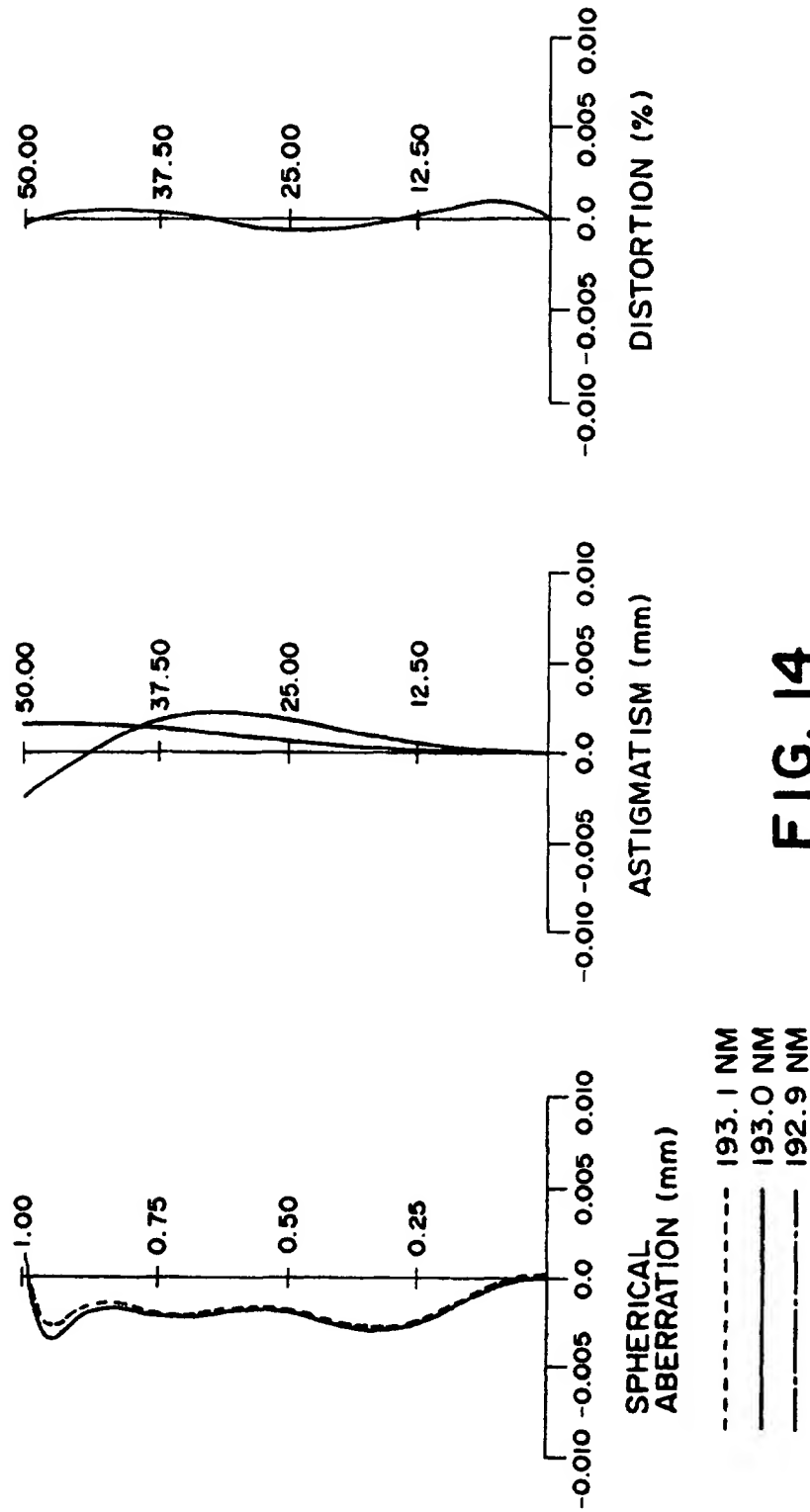


FIG. 14

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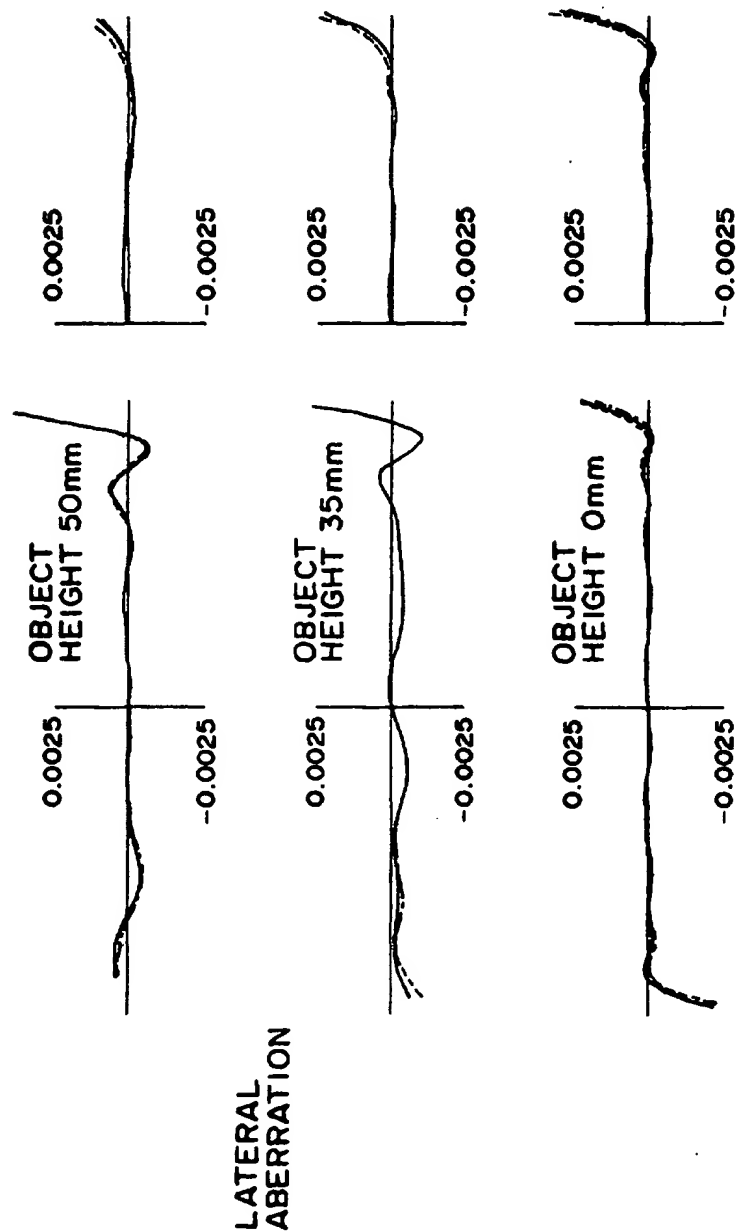


FIG. 15

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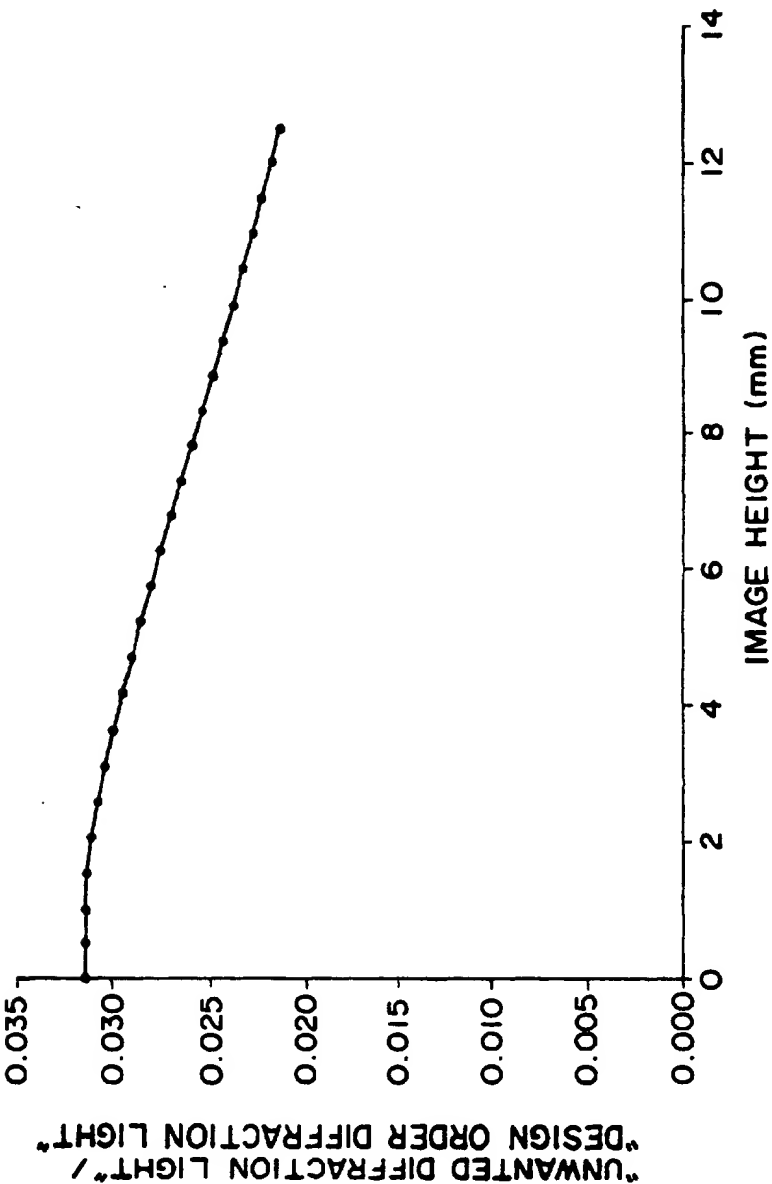


FIG. 16

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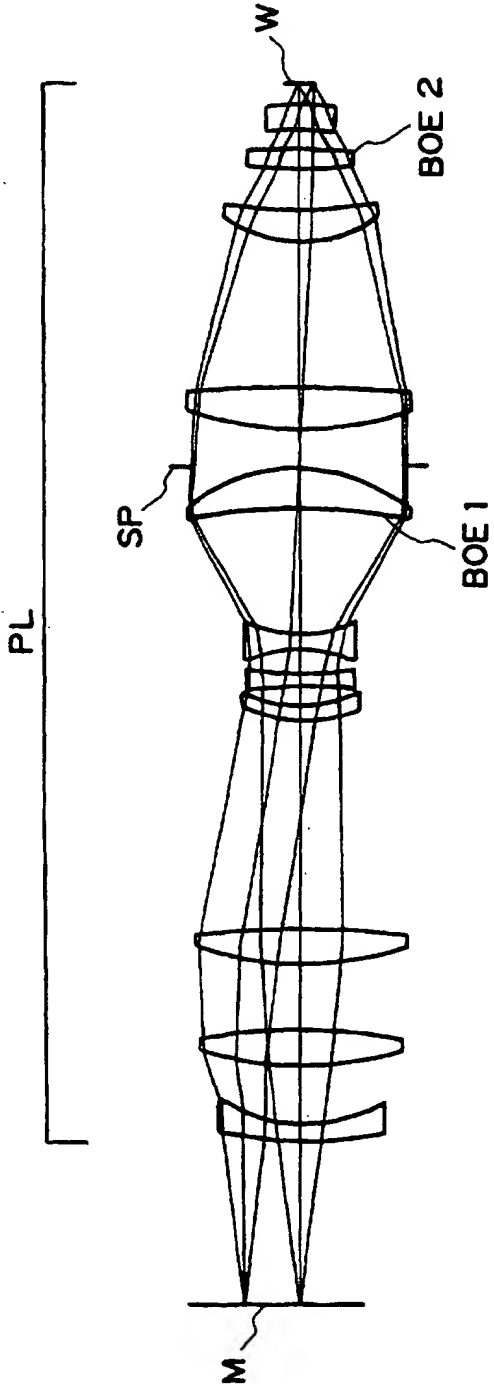


FIG. 17

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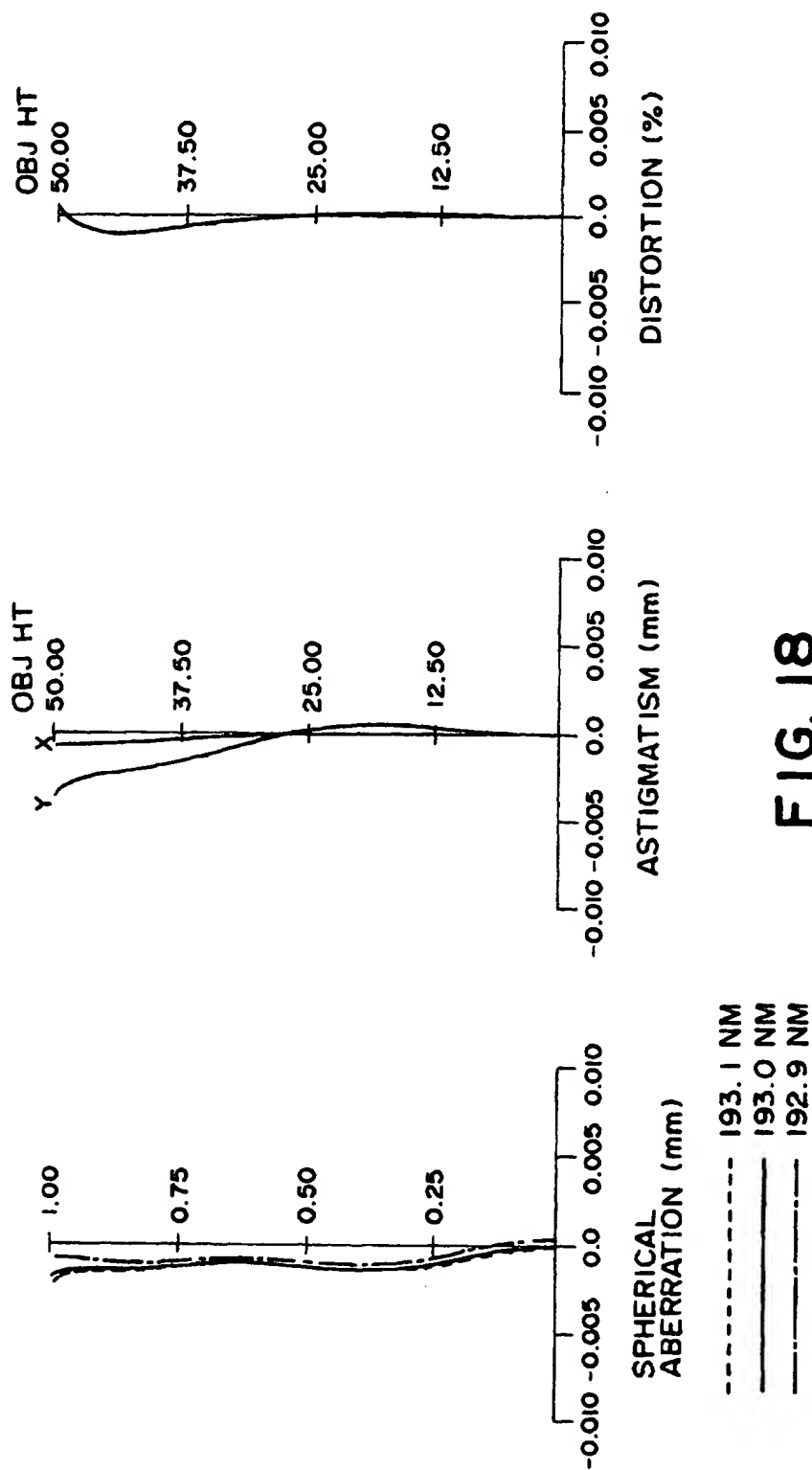


FIG. 18

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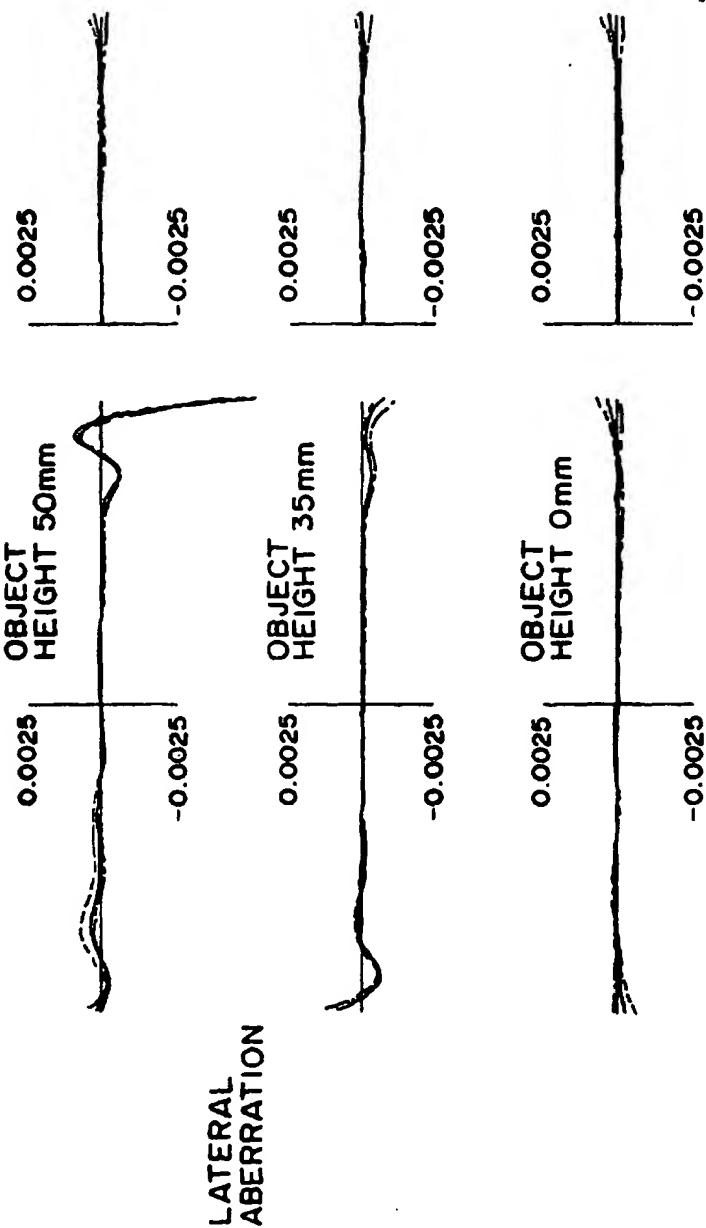


FIG. 19

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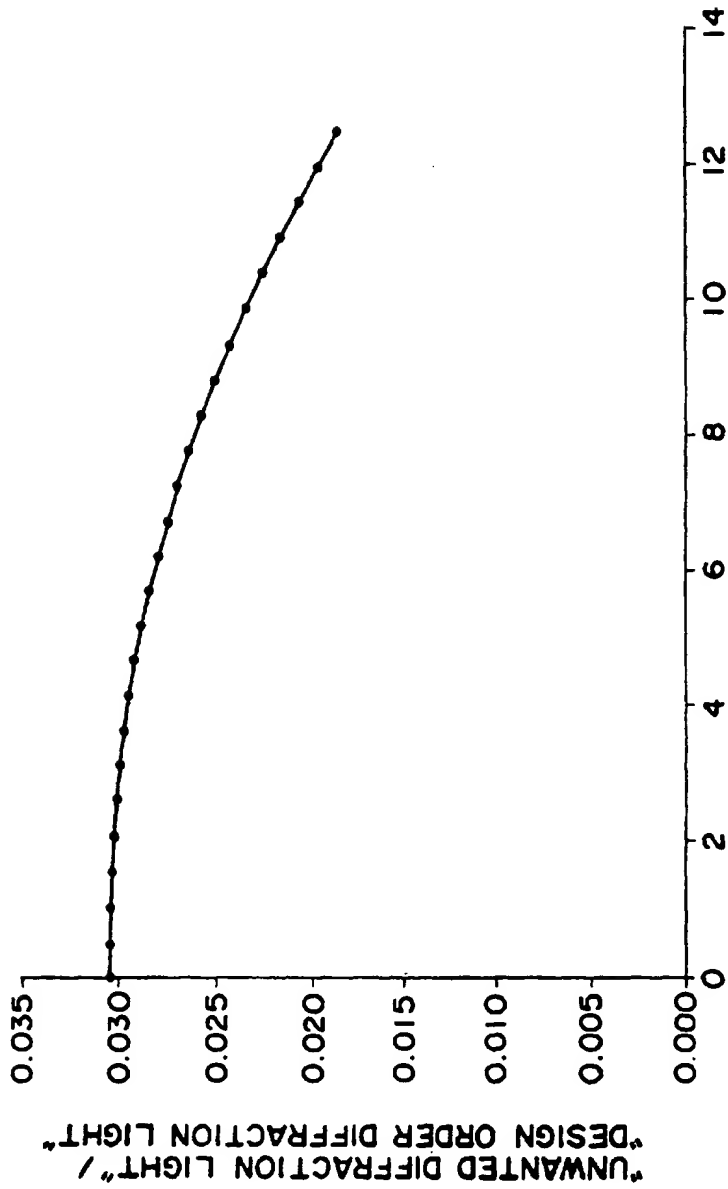


FIG. 20

EP 0 863 440 B1

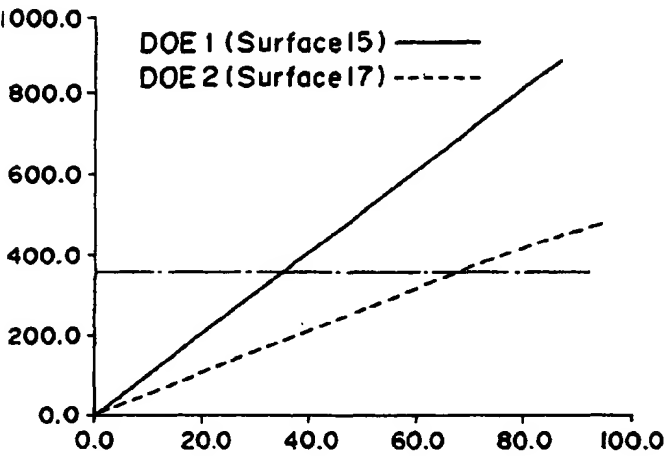


FIG. 21

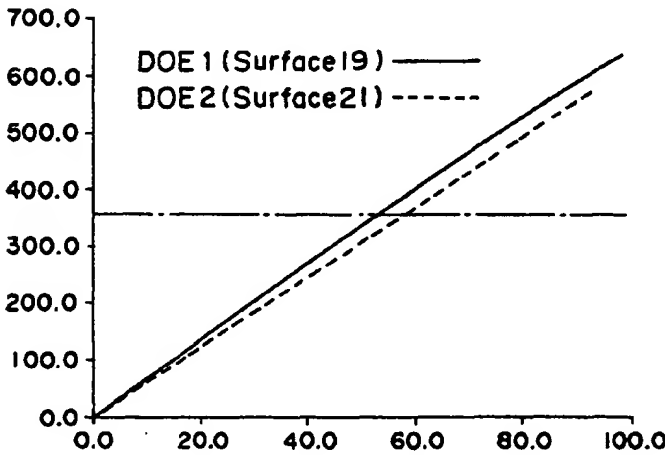


FIG. 22

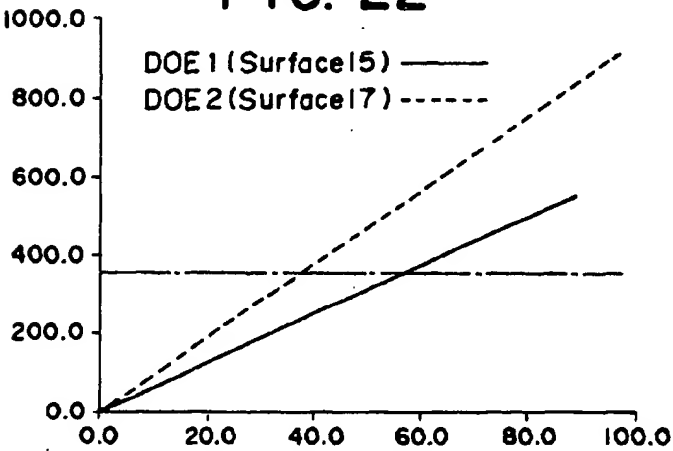


FIG. 23

EP 0 863 440 B1

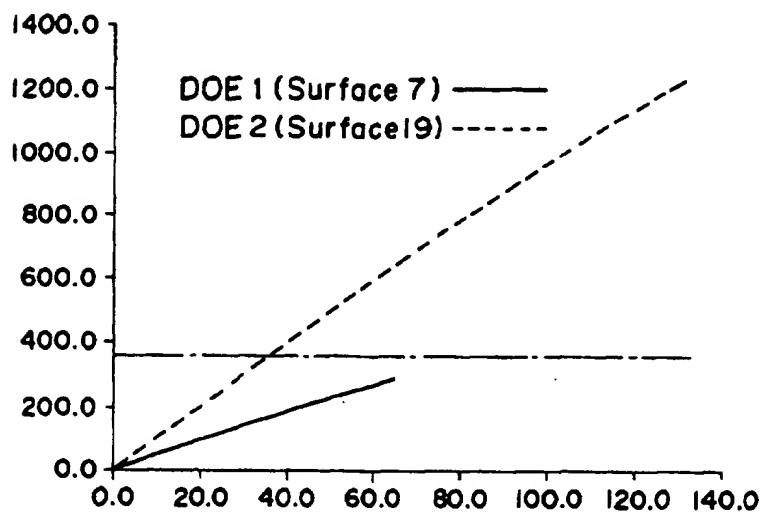


FIG. 24

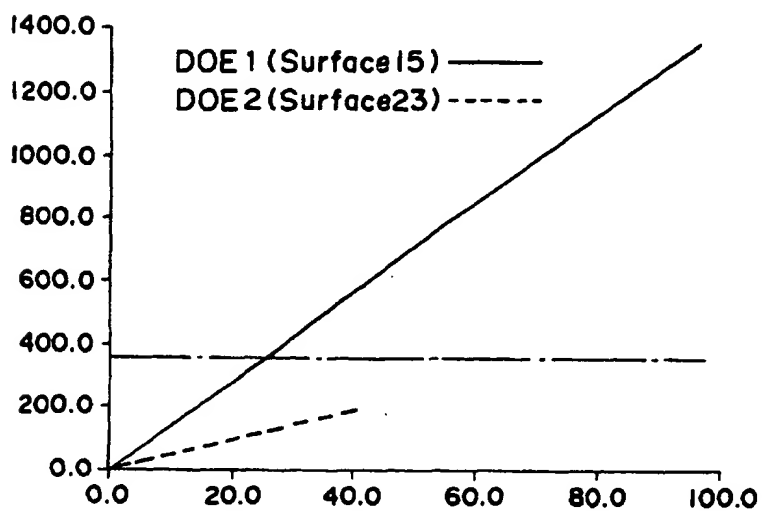


FIG. 25

EP 0 863 440 B1

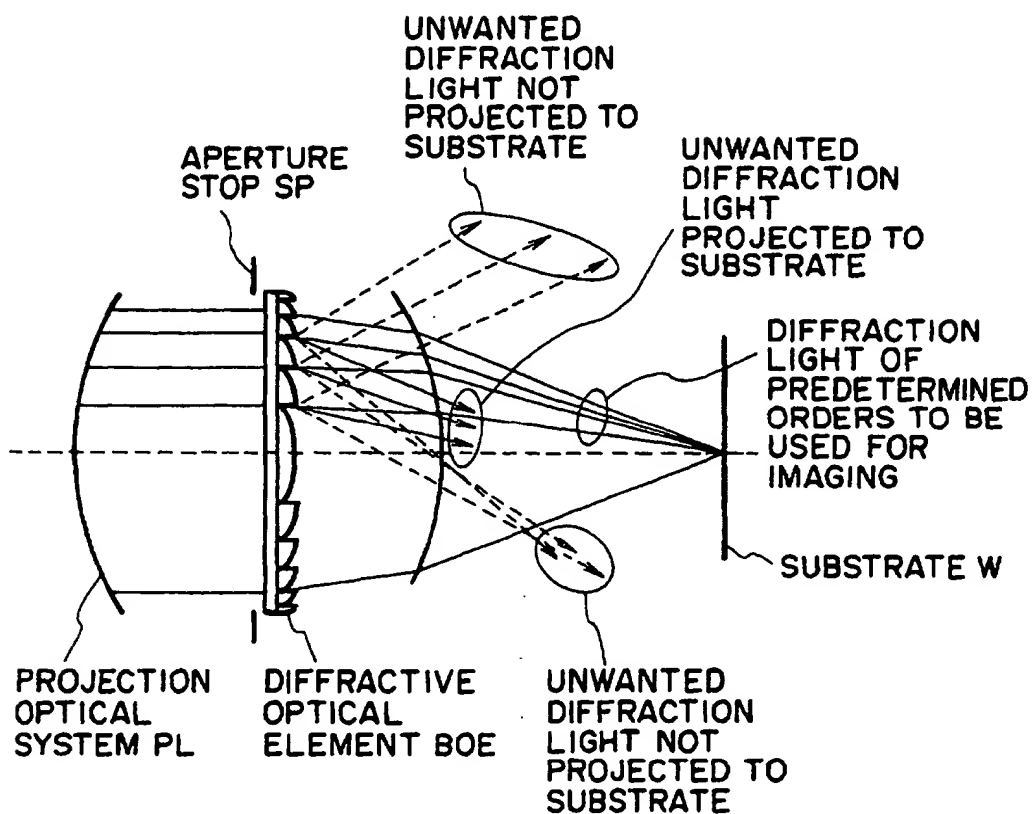


FIG. 26

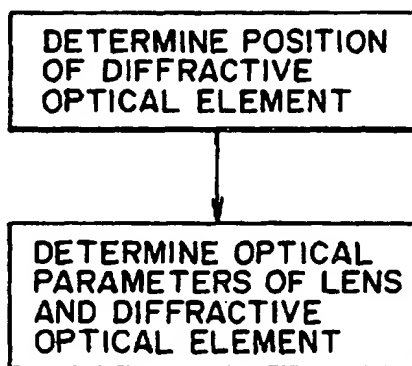


FIG. 27

EP 0 863 440 B1

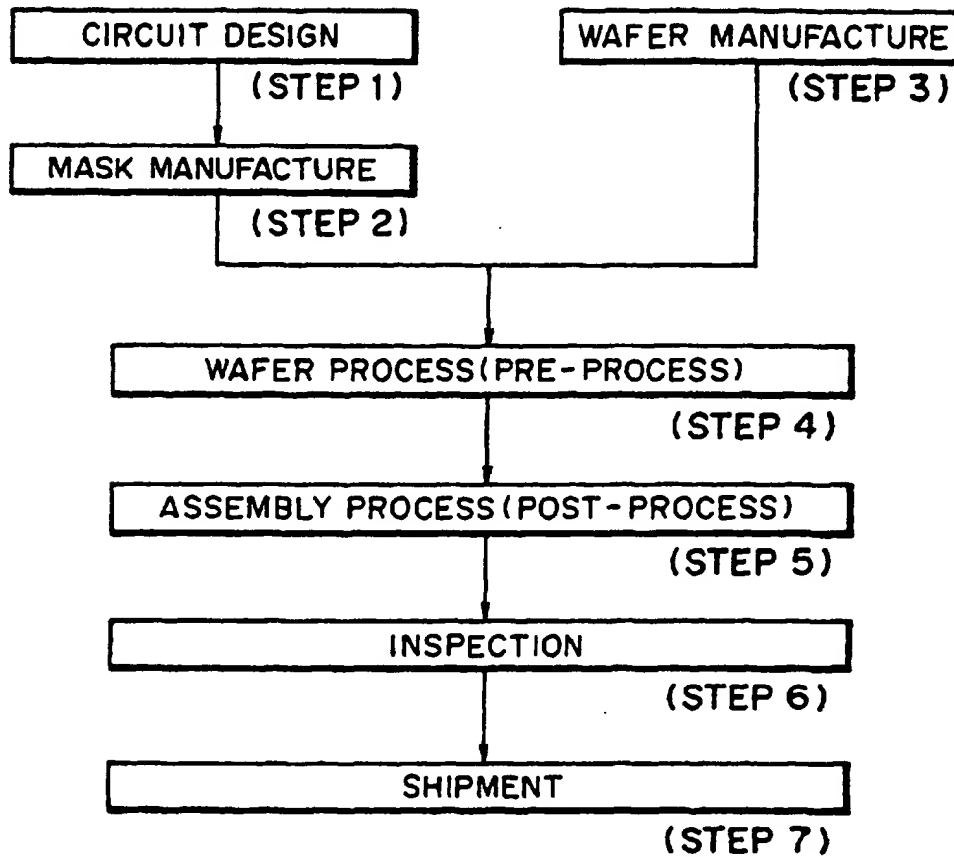


FIG. 28

EP 0 863 440 B1

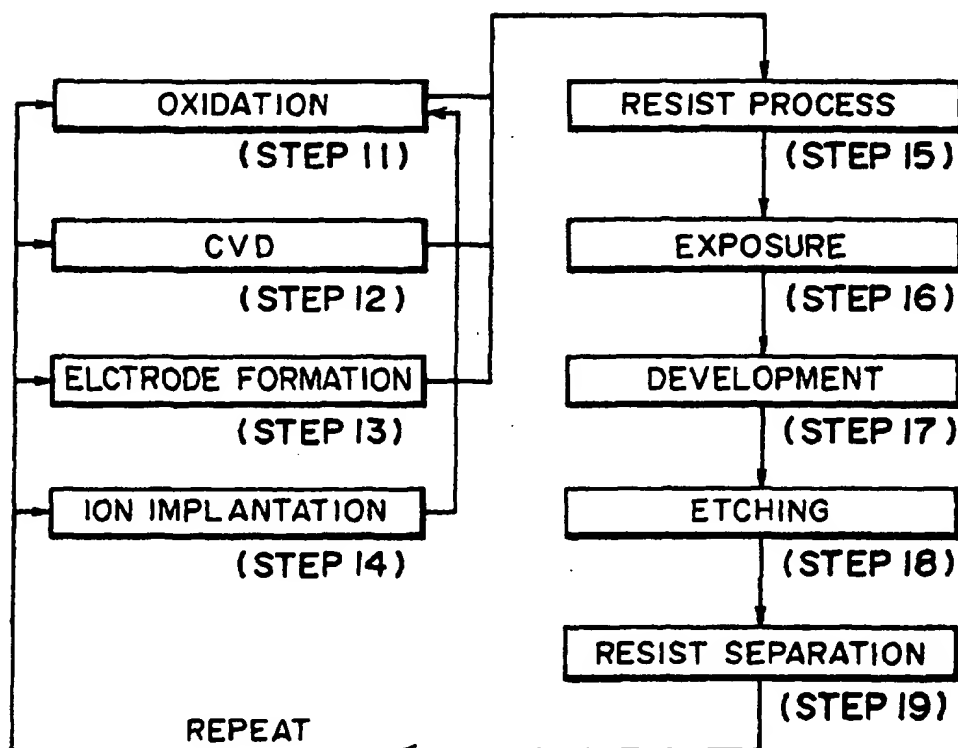


FIG. 29

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